











TPS65218

SLDS206 - NOVEMBER 2014

Power Management for ARM® Cortex™-A8/A9 SOCs and FPGA

Features

- Two Low-Quiescent Current, High Efficiency Stepdown Converters for Battery Backup Domain
 - DCDC5: 1.0 V Output
 - DCDC6: 1.8 V Output
 - VIN Range from 2.2 to 5.5 V
 - Supplied from System Power or Coin-cell **Backup Battery**
- Three Adjustable Step-down Converters with Integrated Switching FETs:
 - DCDC1: 1.1 V Default up to 1.8 A
 - DCDC2: 1.1 V Default up to 1.8 A
 - DCDC3: 1.2 V Default up to 1.8 A
 - VIN Range from 2.7 to 5.5 V
 - Adjustable Output Voltage Range 0.85 to 3.5 V
 - Power Save Mode at Light Load Current
 - 100% Duty Cycle for Lowest Dropout
 - Active Output-Discharge when Disabled
- One Adjustable Buck-boost Converter with Integrated Switching FETs:
 - DCDC4: 3.3 V Default up to 1.0 A
 - VIN Range from 2.7 to 5.5 V
 - Adjustable Output Voltage Range 0.85 to 3.4 V
 - Active Output-discharge when Disabled
- Adjustable General-purpose LDO (LDO1)
 - Default Output 1.8 V
 - VIN Range from 1.8 to 5.5 V
 - Adjustable Output Voltage Range from 0.9 to 3.4 V
 - 400 mA Maximum Current
 - Active Output-Discharge when disabled
- 5 V Load Switch with 100 mA / 500 mA Selectable **Current Limit**
 - VIN Range from 3.0 to 5.5 V
 - 500 mΩ (max) Switch Impedance @ 5 V
- Low Voltage Load Switch with 350 mA Current Limit
 - VIN Range from 1.2 to 3.3 V
 - 110 mΩ (max) Switch Impedance at 1.35 V

- High Voltage Load Switch (LS3) with 100 mA / 500 mA Selectable Current Limit
 - VIN Range from 1.8 to 10.0 V
 - 500 mΩ (max) Switch impedance
- Supervisor with Built-in Supervisor Function Monitors
- Protection, Diagnostics, and Control:
 - Under Voltage Lockout
 - Over Temperature Warning and Shutdown
 - Always-on Push-button Monitor
 - Separate Power-good Output for Backup and Main Supplies
 - Open-drain Interrupt Output Pin
 - I2C Interface (Address 0x24h)

2 Applications

- **Industrial Automation**
- Point of Sale
- Test and Measurement
- Personal Navigation

3 Description

The TPS65218 is a single chip power management IC, specifically designed to support both portable (Lilon battery) and non-portable (5 V adapter) applications. The device is characterized across a -40°C to 105°C temperature range, making it suitable for a wide range of industrial applications.

TPS65218 comes in a 48-pin QFN package (6-mm x 6-mm, .4-mm pitch) and a 48-pin QFP package (7mm \times 7-mm, 0.5-mm pitch).

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TPS65218B1	QFN (48)	6.00 mm × 6.00 mm
TPS65218B1	HTQFP (48)	7.00 mm × 7.00 mm

(1) For all available packages, see the orderable addendum at the end of the datasheet

TEXAS INSTRUMENTS

4 Simplified Schematic

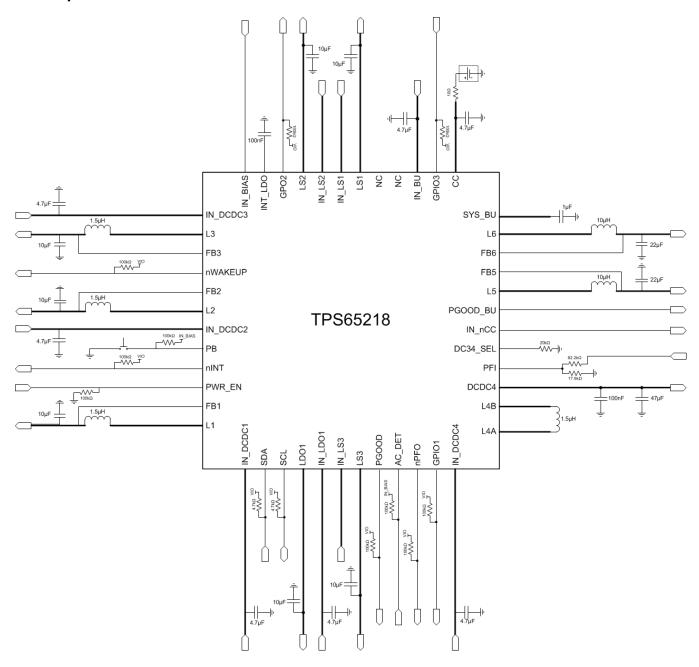




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5 Revision History

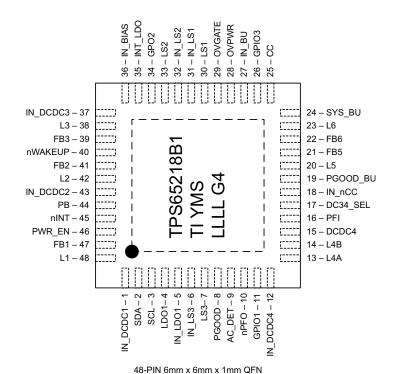
DATE	REVISION	NOTES	
September 2014	*	Initial Release	

TEXAS INSTRUMENTS

6 Pin Configuration and Functions

TPS65218 (TOP VIEW)

TOP VIEW



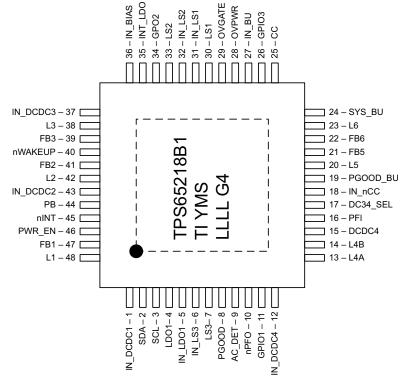
TI = TI LETTERS

YM = YEAR / MONTH DATE CODE

LLLL = LOT TRACE CODE S = ASSEMBLY SITE CODE

O = Pin 1 (MARKED)





48-PIN 9mm x 9mm x 1mm QFP



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
IN DCDC1	1	POWER	Input supply pin for DCDC1
SDA	2	I/O	Data line for the I2C interface. Connect to pull-up resistor.
SCL	3	ı	Clock input for the I2C interface. Connect to pull-up resistor.
LDO1	4	0	Output voltage pin for LDO1. Connect to capacitor.
IN_LDO1	5	POWER	Input supply pin for LDO1
IN_LS3	6	POWER	Input supply pin for load switch 3
LS3	7	0	Output voltage pin for load switch 3. Connect to capacitor
PGOOD	8	0	Power-good output (configured as open drain or push-pull). Pulled low when either DCDC1-4 or LDO1 are out of regulation. Load switches and DCDC5-6 do not affect PGOOD pin.
AC_DET	9	I	Power enable input for DCDC1-4, LDOs and load switches. See state diagram for details. Tie pin to IN_BIAS if not used. Switch pin for DCDC3. Connect to inductor.
nPFO	10	0	Power-fail comparator output, deglitched (open drain). Pin is pulled low when PFI input is below power-fail threshold.
GPIO1	11	I/O	Pin configured as DDR reset-input (driving GPO2) or as general-purpose, open-drain output.
IN_DCDC4	12	POWER	Input supply pin for DCDC4
L4A	13	POWER	Switch pin for DCDC4. Connect to inductor.
L4B	14	POWER	Switch pin for DCDC4. Connect to inductor.
DCDC4	15	POWER	Output voltage pin for DCDC4. Connect to capacitor.
PFI	16	I	Power-Fail comparator input. Connect to resistor divider.
DC34_SEL	17	I	Power-up default selection pin for DCDC3 or DCDC4. Power-up default is programmed by a resistor connected to ground.
IN_nCC	18	0	Output pin indicates if DCDC5 and DCDC6 are powered from main supply (IN_BU) or coin-cell battery (CC).
PGOOD_BU	19	0	Power-good output (push or pull) for battery backup supplies. Pulled low when either DCDC5 or DCDC6 is out of regulation. Pulled high (to DCDC6 output voltage) when both rails are in regulation.
L5	20	POWER	Switch pin for DCDC5. Connect to inductor.
FB5	21	I	Feedback voltage pin for DCDC5. Connect to output capacitor.
FB6	22	I	Feedback voltage pin for DCDC6. Connect to output capacitor.
L6	23	POWER	Switch pin for DCDC6. Connect to inductor.
SYS_BU	24	POWER	System voltage pin for battery-backup supply power path. Connect to capacitor. Connecting any external load to this pin is not recommended.
СС	25	POWER	Coin Cell battery input. Serves as the supply to DCDC5 and DCDC6 if no voltage is applied to IN_BU. Tie this pin to ground if it is not in use.
GPIO3	26	I/O	Pin configured as PMIC reset or general-purpose, open-drain output.
IN_BU	27	POWER	Default input supply pin for battery backup supplies (DCDC5 and DCDC6).
N/C	28	N/A	No connect. Leave pin floating.
N/C	29	N/A	No connect. Leave pin floating.
LS1	30	0	Output voltage pin for load switch 1. Connect to capacitor.
IN_LS1	31	POWER	Input supply pin for load switch 1
IN_LS2	32	I	Input supply pin for load switch 2
LS2	33	0	Output voltage pin for load switch 2. Connect to capacitor.
GPO2	34	0	Pin configured as DDR reset signal (controlled by GPIO1) or as general-purpose output. Buffer can be configured as push-pull or open-drain.
INT_LDO	35	POWER	Internal bias voltage. Connecting any external load to this pin is not recommended.
IN_BIAS	36	POWER	Input supply pin for reference system
IN_DCDC3	37	POWER	Input supply pin for DCDC3
L3	38	POWER	Switch pin for DCDC3. Connect to inductor.
FB3	39	I	Feedback voltage pin for DCDC3. Connect to feedback resistor divider.
nWAKEUP	40	0	Signal to SOC to indicate a power on event (active low, open-drain output)



Pin Functions (continued)

PIN I/O		1/0	DESCRIPTION		
NAME	NO.				
FB2	41	I	Feedback voltage pin for DCDC2. Connect to output capacitor.		
L2	42	POWER	Switch pin for DCDC2. Connect to inductor.		
IN_DCDC2	43	POWER	Input supply pin for DCDC2		
РВ	44	ı	Push-button monitor input. Typically connected to a momentary switch to ground (active low). See state diagram for details.		
nINT	45	0	Interrupt output (active low, open drain). Pin is pulled low if an interrupt bit is set. The returns to HiZ state after the bit causing the interrupt has been read. Interrupts can be masked.		
PWR_EN	46	I	Power enable input for DCDC1-4, LDOs and load switches. See state diagram for details.		
FB1	47	I	Feedback voltage pin for DCDC1. Connect to output capacitor.		
L1	48	POWER	Switch pin for DCDC1. Connect to inductor.		
POWERPAD	N/A	POWER	Power ground and thermal relief. Connect to ground plane.		

7 Specifications

7.1 Absolute Maximum Ratings

Operating under free-air temperature range (unless otherwise noted) (1)

		MIN	MAX	UNIT
	IN_BIAS, IN_LDO1, IN_LS, IN_DCDC1, IN_DCDC2, IN_DCDC3, IN_DCDC4	-0.3	7	
Supply voltage	IN_LS1, CC	-0.3	3.6	V
range	IN_LS3	-0.3	11.2	
	IN_BU	-0.3	5.8	
lancet colleges assessed	DC34_SEL	-0.3	3.6	
Input voltage range	All pins unless specified separately	-0.3	7	.,
Output voltage	DC34_SEL	-0.3	3.6	V
range	All pins unless specified separately	-0.3	7	
Source or sink	GPO2		6	
current	PGOOD_BU, IN_nCC		1	mA
Sink current	PGOOD, nWAKEUP, nINT, nPFO, SDA, GPIO1, GPIO3		6	mA
T _A Operating ambient	temperature range	-40	105	°C
T _J Junction temperatu	re range	-40	125	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

7.2 Handling Ratings

		MIN	MAX	UNIT
T _{stg}	Storage temperature range	- 65	150	°C
V _(ESD)	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins (1)	-2000	2000	V
	Charged device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	– 500	500	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	TYP MAX	UNIT
Supply voltage, IN_BIAS	2.7	5.5	V

Recommended Operating Conditions (continued)

over operating free-air temperature range (unless otherwise noted)

	MIN	TYP MAX	UNIT
Input voltage range for DCDC1, DCDC2, DCDC3, DCDC4	2.7	5.5	V
Supply voltage, IN_BU	2.2	5.5	V
Supply voltage, CC	2.2	3.3	V
Input voltage range for LDO1	1.8	5.5	V
Input voltage range for LS1	1.2	3.3	V
Input voltage range for LS2	3.0	5.5	V
Input voltage range for LS3	1.8	9.9	V
Output voltage range for DCDC1, DCDC2, DCDC3, DCDC4	0.85	3.5	V
Output voltage range for DCDC5	1.0	1.1	V
Output voltage range for DCDC6	1.8	1.8	V
Output voltage range for LDO1	0.9	3.4	V
Output current DCDC1, DCDC2, DCDC3	0	1.8	Α
Output current DCDC4	0	1.0	Α
Output current DCDC5, DCDC6	0	10	mA
Output current LDO1	0	400	mA
Output current LS1	0	300	mA
Output current LS2	0	1000	mA
Output current LS3	0	1000	mA

7.4 Thermal Information

		PV	V	UNIT
	THERMAL METRIC	16 PI	INS	
		RSL	PHP	
$R_{\theta JC}$	Junction-to-case (top)	17.2	13.3	
$R_{\theta JB}$	Junction-to-board	5.8	7.9	
$R_{\theta JA}$	Thermal resistance, junction to ambient. JEDEC 4layer high-K board	30.6	26.7	°C/W
Ψ_{JT}	Junction-to-package top	0.2	0.3	
Ψ_{JB}	Junction-to-board	5.6	7.8	
$R_{\theta JC}$	Junction-to-case (bottom)	1.5	0.7	

7.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITION	ONS	MIN	TYP	MAX	UNIT
INPUT VO	LTAGE AND CURRENTS						
V _{IN_BIAS}	Input supply voltage range	Normal operation		2.7	7 5.5		V
		EEPROM programming		4.5		5.5	V
V _{UVLO} Under voltage I	Under voltage lock-out	Measured in respect to V _{IN_BIAS} ;	UVLO[1:0] = 00	2.7	2.75	2.8	
			UVLO[1:0] = 01	2.85	2.95	3.05	V
			UVLO[1:0] = 10	3.15	3.25	3.35	
		UVLO[1:0] = 11	3.25	3.35	3.45		
	Hysteresis	Supply rising	UVLOHYS=0		200		\/
			UVLOHYS=1		400		mV
	Deglitch time				5		ms
I _{OFF}	OFF state current, Total current into IN_BIAS, IN_DCDCx, IN_LDO1, IN_LSx, IN_BU	V_{IN} = 3.6 V; All rails disabled. T_J = 085°C.			5		μΑ

TEXAS INSTRUMENTS

Electrical Characteristics (continued)

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST C	CONDITIONS	MIN	TYP	MAX	UNIT
I _{SUSPEND}	SUSPEND Current Total current into IN_BIAS, IN_DCDCx, IN_LDO1, IN_LSx, IN_BU	V _{IN} = 3.6 V; DCDC3 er load. All other rails disabled. T _J = 0105°C	nabled, low-power mode, no		220		μА
INT_LDO				I.			
V _{OUT}	Output voltage				2.5		V
	DC Accuracy	I _{OUT} < 10 mA		-2%		2%	
I _{OUT}	Output current range	Maximum allowable exte	ernal load	0		10	mA
I _{LIMIT}	Short circuit current limit	Output shorted to GND			23		mA
t _{HOLD}	Hold-up time	Measured from V_{IN_BIAS} All rails enabled. $V_{IN_BIAS} = 2.8 \text{ V to 0 in} < \text{No external load on INT}_{COUT} = 22 \mu\text{F}$		150			ms
C _{OUT}	Nominal output capacitor value	Ceramic, X5R or X7R		0.1		22	μF
	Tolerance			-20%		20%	<u> </u>
DCDC1, D	CDC2 (1.1 V BUCK)	1		l		1.	
V _{IN_DCDC1} ,	Input voltage range	V _{IN_BIAS} > 2.7 V		2.7		5.5	V
V _{DCDC1,2}	Output voltage range	Adjustable through I ² C		0.85		1.65	V
	DC Accuracy	$2.7 \text{ V} \le \text{V}_{\text{IN}} \le 5.5 \text{ V}; 0 \text{ A} \le \text{I}_{\text{OUT}} \le 1.8 \text{ A}$		-2%		2%	
I _{OUT}	Continuous output current	V _{IN_DCDC1,2} > 2.8 V				1.8	Α
IQ	Quiescent current	Total current from I _{N_DCE} switching, no load	_{DC1,2} pin; Device not		25	50	μΑ
R _{DS(ON)}	High-side FET ON-resistance	$V_{IN_DCDC1,2} = 3.6 \text{ V}$			230	355	m0
	Low-side FET ON-resistance	$V_{IN_DCDC1,2} = 3.6 \text{ V}$			90	145	mΩ
I _{LIMIT}	High-side current limit	$V_{IN_DCDC1,2} = 3.6 \text{ V}$			2.8		Α
	Low-side current limit	$V_{IN_DCDC1,2} = 3.6 \text{ V}$			3.1		Α
V_{PG}	Power-good threshold	V _{OUT} falling	STRICT=0	86%	90%	94%	
			STRICT=1	96%	96.5%	97%	
	Hysteresis	V _{OUT} rising	STRICT=0	3%	4%	5%	
			STRICT=1		0.25%		
	Deglitch	V _{OUT} falling	STRICT=0		1		ms
			STRICT=1		50		
		V _{OUT} rising	STRICT=0		10		μs
			STRICT=1		10		
	Time-out				5		ms
V_{OV}	Over-voltage detection threshold (1)	V _{OUT} rising		103%	103.5%	104%	
	Hysteresis	V _{OUT} falling		0.25%			
	Deglitch	V _{OUT} rising			50		μs
I _{INRUSH}	Inrush current	V _{IN_DCDC1,2} = 3.6 V; C _{OL}	_T =10100°F			500	mA
R _{DIS}	Discharge resistor			150	250	350	Ω
L	Nominal inductor value			1.0	1.5	2.2	μH
	Tolerance			-30%		30%	

⁽¹⁾ Over-voltage is monitored only if STRICT =1.

Electrical Characteristics (continued)

over operating free-air temperature range (unless otherwise noted)

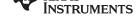
	PARAMETER	TEST CO	ONDITIONS	MIN	TYP	MAX	UNIT
C _{OUT}	Nominal output capacitor value	Ceramic, X5R or X7R				500	μF
	Tolerance			-20%		20%	
DCDC3 (1.	2 V BUCK)			·			
V _{IN_DCDC3}	Input voltage range	$V_{IN_BIAS} > 2.7 \text{ V}$		2.7		5.5	V
V_{DCDC3}	Output voltage range	Adjustable through I ² C		0.9		3.4	V
	DC Accuracy	$2.7 \text{ V} \le \text{V}_{\text{IN}} \le 5.5 \text{ V}; 0 \text{ A} \le$	≤ I _{OUT} ≤ 1.8 A	-2%		2%	
I _{OUT}	Continuous output current	V _{IN_DCDC3} > 2.8 V				1.8	Α
l _Q	Quiescent current	Total current from IN_DC switching, no load	DC3 pin; Device not		25	50	μΑ
R _{DS(ON)}	High-side FET ON-resistance	$V_{IN_DCDC3} = 3.6 \text{ V}$			230	345	mΩ
	Low-side FET ON-resistance	$V_{IN_DCDC3} = 3.6 \text{ V}$			100	150	11122
I _{LIMIT}	High-side current limit	$V_{IN_DCDC3} = 3.6 \text{ V}$			2.8		Α
	Low-side current limit	$V_{IN_DCDC3} = 3.6 \text{ V}$			3		
V_{PG}	Power-good threshold	V _{OUT} falling	STRICT = 0	86%	90%	94%	
			STRICT = 1	95%	95.5%	96%	
	Hysteresis	V _{OUT} rising	STRICT = 0	3%	4%	5%	
			STRICT = 1		0.25%		
	Deglitch	V _{OUT} falling	STRICT = 0		1		ms
			STRICT = 1		50		
		V _{OUT} rising	STRICT = 0		10		μs
			STRICT = 1		10		
	Time-out				5		ms
V _{OV}	Over-voltage detection threshold (1)	V _{OUT} rising		104%	104.5%	105%	
	Hysteresis	V _{OUT} falling			0.25%		
	Deglitch	V _{OUT} rising			50		μs
I _{INRUSH}	Inrush current	$V_{IN_DCDC3} = 3.6 \text{ V; } C_{OUT}$	=10100 μF			500	mA
R _{DIS}	Discharge resistor			150	250	350	Ω
L	Nominal inductor value			1.0	1.5	2.2	μH
	Tolerance			-30%		30%	
C _{OUT}	Nominal output capacitor value	Ceramic, X5R or X7R		10		100	μF
	Tolerance			-20%		20%	
DCDC4 (3.	3 V BUCK-BOOOST)						
V _{IN_DCDC4}	Input voltage range	V _{IN_BIAS} > 2.7 V		2.7		5.5	V
V_{DCDC4}	Output voltage range	Adjustable through I ² C		1.175		3.4	V
	DC Accuracy	$2.7 \text{ V} \le \text{V}_{\text{IN}} \le 5.5 \text{ V}; 0 \text{ A} \le$	≤I _{OUT} ≤ 1 A	-2		2	
	Minimum duty cycle in step- down mode					18%	
I _{OUT}	Continuous output current	V _{IN_DCDC4} = 2.8 V, V _{OUT}	= 3.3 V			1.0	
		V _{IN_DCDC4} = 3.6 V, V _{OUT}				1.3	Α
		$V_{IN_DCDC4} = 5.0 \text{ V}, V_{OUT} = 0.0 \text{ V}$				1.6	
IQ	Quiescent current	Total current from IN_DC switching, no load			25	50	μA
f _{SW}	Switching frequency				2400		kHz

NSTRUMENTS

Electrical Characteristics (continued)

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDIT	IONS	MIN	TYP	MAX	UNIT
R _{DS(ON)}	High-side FET ON-resistance	$V_{IN_DCDC3} = 3.6 \text{ V}$	IN_DCDC4 to L4A		166		
			L4B to DCDC4		149		~ 0
	Low-side FET ON-resistance	V _{IN_DCDC3} = 3.6 V	L4A to GND		142	190	mΩ
			L4B to GND		144	190	
I _{LIMIT}	Average switch current limit	$V_{IN_DCDC4} = 3.6 \text{ V}$,		3000		mA
V_{PG}	Power-good threshold	V _{OUT} falling	STRICT = 0	86%	90%	94%	
			STRICT = 1	95%	95.5%	96%	
	Hysteresis	V _{OUT} rising	STRICT = 0	3%	4%	5%	
			STRICT = 1		0.25%		
	Deglitch	V _{OUT} falling	STRICT = 0		1		ms
			STRICT = 1		50		
		V _{OUT} rising	STRICT = 0		10		μs
			STRICT = 1		10		·
	Time-out				5		ms
V _{OV}	Over-voltage detection threshold (1)	V _{OUT} rising		104%	104.5%	105%	
	Hysteresis	V _{OUT} falling			0.25%		
	Deglitch	V _{OUT} rising			50		μs
I _{INRUSH}	Inrush current	V _{IN_DCDC4} = 3.6 V; C _{OUT} =10100μF				500	mA
R _{DIS}	Discharge resistor	·		150	250	350	Ω
L	Nominal inductor value			1.2	1.5	2.2	μH
	Tolerance			-30%		30%	-
C _{OUT}	Nominal output capacitor value	Ceramic, X5R or X7R		40		100	μF
	Tolerance			-20%		20%	-
DCDC5,6	POWER PATH			1			
V _{CC}	DCDC5, 6 input voltage range	$V_{IN BU} = 0$		2.2		3.3	V
$V_{\text{IN_BU}}$	DCDC5, 6 input voltage range ⁽²⁾	0 < V _{CC < 5.5 V}		2.2		5.5	V
T _{RISE}	V _{CC} , V _{IN_BU} rise time	Voltage rising from 0 V to 5.5 V	r	30			μs
R _{DS(ON)}	Power path switch impedance	CC to SYS BU			14.5		
, ,		$V_{CC} = 2.4 \text{ V}, V_{IN_BU} = 0 \text{ V}$					
	Power path switch impedance				10.5		Ω
	. ener paur ennen impedance	IN_BU to SYS_BU			. 0.0		
1	Forward leakage current	V _{IN_BU} = 3.6 V			50	300	
I _{LEAK}	i orward leakage current	Into CC pin;			30	300	
		$V_{CC} = 3.3 \text{ V}, V_{IN_BU} = 0;$					
		OFF state; FSEAL = 0; over full temperature range					~ Λ
	Reverse leakage current					500	nA
	Neverse leakage current	Out of CC pin;				300	
		$V_{CC} = 1.5 \text{ V}; V_{IN_BU} = 5.5 \text{ V};$					
	A	over full temperature range				4000	
R _{CC}	Acceptable CC source impedance	$I_{OUT, DCDC5} < 10 \mu A;$				1000	Ω
		I _{OUT, DCDC6} < 10 μA					



Electrical Characteristics (continued)

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _Q	Quiescent current	Average current into CC pin; RECOVERY or POWER_OFF state; V _{IN_BU} = 0; V _{CC} = 2.4 V DCDC5 and DCDC6 enabled, no load T _J =25 °C		350		nA
DCDC5 (1	.0 V BATTERY BACKUP SUPPLY					
V _{DCDC5}	Output Voltage			1		V
	DC Accuracy	2.7 V ≤ V _{IN_BU} ≤ 5.5 V; 1 uA ≤ I _{OUT} ≤ 25 mA	-1.5%		1.5%	
	Output voltage ripple	L=10 μH; C _{OUT} = 22 μF; 100 μA load			32	mV_{pp}
I _{OUT}	Continuous output current	2.2 V < V _{CC} < 3.3 V V _{IN_BU} = 0 2.7 V < V _{IN_BU} < 5.5 V		10	100	μA mA
R _{DS(ON)}	High-side FET ON-resistance	$V_{\text{IN_BU}} = 2.8V$		2.5	3.5	III/A
. 109(ON)	Low-side FET ON-resistance	V _{IN_BU} = 2.8V		2.3	3.3	Ω
I _{LIMIT}	High-side current limit	V _{IN_BU} = 2.8V		50	3	mA
V _{PG}	Power-good threshold	V _{OUT} falling	79%	85%	91%	шл
* PG	Hysteresis	V _{OUT} rising	7.570	6%	0170	
Impuou	Inrush current	$V_{CC} = 3.0 \text{ V}; V_{IN BU} = 0; C_{OUT} = 1047 \mu\text{F}$		070	500	μΑ
I _{INRUSH}	Nominal inductor value	Chip Inductor	4.7	10	22	μH
_	Tolerance	Stap inductor	-30%	10	30%	μιι
C _{OUT}	Nominal output capacitor value	Ceramic, X5R or X7R	20		47	μF
C 001	Tolerance	Ceramic, ASIC OF ATIC	-20%		20%	μι
DCDC6 (1	.8 V BATTERY BACKUP SUPPLY	<u> </u>	-2070		2070	
	Output voltage) 		1.8		V
V_{DCDC6}	DC Accuracy	2.7 V ≤ V _{IN BU} ≤ 5.5 V; 1 uA ≤ I _{OUT} ≤ 25 mA	-1.5%	1.0	1.5%	v
	Output voltage ripple	L=10 µH; C _{OUT} = 22 µF; 100 µA load	-1.576		30	m\/
1	Continuous output current			10	100	mV_{pp}
Гоит	Continuous output current	$2.2 \text{ V} < \text{V}_{CC} < 3.3 \text{ V}$ $\text{V}_{IN_BU} = 0$		10	100	μΑ
R _{DS(ON)}	High-side FET ON-resistance	$V_{IN_BU} = 3.0 \text{ V}$		2.5	3.5	0
	Low-side FET ON-resistance	V _{IN_BU} = 3.0 V		2	3	Ω
I _{LIMIT}	High-side current limit	V _{IN_BU} = 3.0 V		50		mA
V_{PG}	Power-good threshold	V _{OUT} falling	87%	91%	95%	-
	Hysteresis	V _{OUT} rising		3%		
I _{INRUSH}	Inrush current	$V_{CC} = 3.0 \text{ V}; V_{IN_BU} = 0; C_{OUT} = 1047 \mu\text{F}$			500	μΑ
L	Nominal inductor value	Chip Inductor	4.7	10	22	μΗ
	Tolerance		-30%		30%	
C _{OUT}	Nominal output capacitor value	Ceramic, X5R or X7R	20		47	μF
	Tolerance		-20%		20%	
LDO1 (1.8	3 V LDO)					
V_{IN_LDO1}	Input voltage range	$V_{IN_BIAS} > 2.7 \text{ V}$	1.8		5.5	V
IQ	Quiescent current	No load		35		μΑ
V _{OUT}	Output voltage range	Adjustable through I ² C	0.9		3.4	V
	DC Accuracy	$V_{OUT}+0.2 \text{ V} \le V_{IN} \le 5.5 \text{ V}; 0 \text{ A} \le I_{OUT} \le 200 \text{ mA}$	-2%		2%	
I _{OUT}	Output current range		0		200	m ^
1001		V _{IN_LDO1} >2.7 V, V _{OUT} =1.8 V	0	-	400	mA

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Electrical Characteristics (continued)

over operating free-air temperature range (unless otherwise noted)

ovor opor	PARAMETER	TEST CONE	DITIONS	MIN	TYP	MAX	UNIT
I _{LIMIT}	Short circuit current limit	Output shorted to GND		490	550		mA
V _{DO}	Dropout voltage	I _{OUT} = 100 mA, V _{IN} = 3.6 V				200	mV
V _{PG}	Power-good threshold	V _{OUT} falling	STRICT = 0	86%	90%	94%	
- FG	· · · · · · · · · · · · · · · · · · ·	1001 129	STRICT = 1	95%	95.5%	96%	
		Hysteresis, V _{OUT} rising	STRICT = 0	3%	4%	5%	
		, , , , ,	STRICT = 1		0.25%		
	Deglitch	V _{OUT} falling	STRICT = 0		1		ms
	-		STRICT = 1		50		
		V _{OUT} rising	STRICT = 0		10		μs
			STRICT = 1		10		
	Time-out				5		ms
V _{OV}	Over-voltage detection threshold (1)	V _{OUT} rising		104%	104.5%	105%	
	Hysteresis	V _{OUT} falling			0.25%		
	Deglitch	V _{OUT} rising			50		μs
		V _{OUT} falling			1		ms
R _{DIS}	Discharge resistor			150	250	350	Ω
C_OUT	Nominal output capacitor value	Ceramic, X5R or X7R		10		100	μF
	Tolerance			-20%		20%	
LOAD SW	ITCH 1 (LS1)						
V _{IN_LS1}	Input voltage range	V _{IN_BIAS} > 2.7 V		1.2		3.3	V
R _{DS(ON)}	Static on-resistance	V _{IN_LS1} = 1.8 V, I _{OUT} =300 m/ _I DDR2 / LPDDR / MDDR temperature range				110	
		V _{IN_LS1} = 1.5 V, I _{OUT} =300 mA, DDR3 @ 333MHz over full temperature range V _{IN_LS1} = 1.35 V, I _{OUT} =300 mA, DDR3L @ 333MHz over full temperature range V _{IN_LS1} = 1.2 V, I _{OUT} =200 mA, LPDDR2 @ 333MHz over full temperature range				110	mΩ
						110	
						150	
I _{LIMIT}	Short circuit current limit	Output shorted to GND		350			mA
t _{BLANK}	Interrupt blanking time	Output shorted to GND until	interrupt is triggered		15		ms
R _{DIS}	Internal discharge resistor at output ⁽³⁾			150	250	350	Ω
T _{OTS}	Over temperature shutdown (4)	uutdown ⁽⁴⁾		125	132	139	°C
	Hysteresis				10		<u></u>
C _{OUT}	Nominal output capacitor value	Ceramic, X5R or X7R		10		100	μF
	Tolerance			-20%		20%	
LOAD SW	ITCH 2 (LS2)					ı	
V _{IN_LS2}	Input voltage range	$V_{IN_BIAS} > 2.7 \text{ V}$		4.0		5.5	V
V_{UVLO}	Under voltage lock-out	Measured at IN_LS2. Supply	falling (5)	2.48	2.60	2.70	V
	Hysteresis	Input voltage rising			170		mV
R _{DS(ON)}	Static on-resistance	$V_{IN_LS2} = 5.0 \text{ V}, I_{OUT} = 500 \text{ m/s}$ range	V _{IN_LS2} = 5.0 V, I _{OUT} =500 mA, over full temperature			500	mΩ

Discharge function disabled by default. Switch is temporarily turned OFF if temperature exceeds OTS threshold. Switch is temporarily turned OFF if input voltage drops below UVLO threshold. (5)



Electrical Characteristics (continued)

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDI	TIONS	MIN	TYP	MAX	UNIT
I _{LIMIT}	Short circuit current limit	Output shorted to GND;	LS2ILIM[1:0] = 00	100		126	
		V _{IN_LS2} >4.0 V	LS2ILIM[1:0] = 10	200		251	
			LS2ILIM[1:0] = 01	500		631	mA
			LS2ILIM[1:0] = 11	1000		1290	
I _{LEAK}	Reverse leakage current	V _{LS2} >V _{IN LS2} +1 V			12	30	μA
t _{BLANK}	Interrupt blanking time	Output shorted to GND until in	terrupt is triggered		15		ms
R _{DIS}	Internal discharge resistor at output (3)					380	Ω
T _{OTS}	Over temperature shutdown (5)			125	132	139	00
	Hysteresis				10		٥C
C _{OUT}	Nominal output capacitor value	Ceramic, X5R or X7R		1		100	μF
	Tolerance			-20%		20%	
LOAD SW	TITCH 3 (LS3)						
V _{IN_LS3}	Input voltage range	V _{IN BIAS} > 2.7 V		1.8		10.0	V
R _{DS(ON)} Static on-resistance		V _{IN_LS3} = 9.0 V, I _{OUT} = 500 mA range	over full temperature			440	
		V_{IN_LS3} = 5.0 V, I_{OUT} = 500 mA, over full temperature range				526	_
		V_{IN_LS3} = 2.8 V, I_{OUT} = 200 mA, over full temperature range				656	mΩ
		V _{IN_LS3} = 1.8 V, I _{OUT} = 200 mA range	over full temperature			910	
I _{LIMIT} Short circuit current limit		Output shorted to GND	LS3ILIM[1:0] = 00	100		126	
LIVIII			LS3ILIM[1:0] = 10	200		253	m^
		LS3ILIM[1:0] = 01		500		738	mA
			LS3ILIM[1:0] = 11	1000		1234	
t _{BLANK}	Interrupt blanking time	Output shorted to GND until in	terrupt is triggered		15		ms
R _{DIS}	Internal discharge resistor at output (3)			650	1000	1500	Ω
T _{OTS}	Over temperature shutdown (5)			125	132	139	
	Hysteresis				10		٥C
C _{OUT}	Nominal output capacitor value	Ceramic, X5R or X7R		1	100	220	μF
	Tolerance			-20%		20%	
BACKUP	BATTERY MONITOR	+					
V _{TH}	Comparator threshold	Ideal level			3.00		
		Good level			2.60		V
		Low level			2.30		
	Accuracy			-3%		3%	
R _{LOAD}	Load impedance	Applied from CC to GND durin	g comparison	70	100	130	kΩ
t _{DLY}	Measurement delay	R _{LOAD} is connected during delayis taken at the end of delay.	ay time. Measurement		600		ms
VO LEVEL	S AND TIMING CHARACTERIST	cs		1			
PG _{DLY}	PGOOD delay time	PGDLY[1:0] = 00			10		
	•	PGDLY[1:0] = 01			20		
		PGDLY[1:0] = 10			50		ms
		PGDLY[1:0] = 11			150		

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Electrical Characteristics (continued)

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT	
t _{DG}	Deglitch time	PB input	Rising edge		100			
			Falling edge		50		ms	
		AC_DET input	Rising edge		100		μs	
			Falling edge		10		ms	
		PWR_EN input	Rising edge		10		ms	
			Falling edge		100		μs	
		GPIO1	Rising edge		1			
			Falling edge		1		ms	
		GPIO3 Rising edge			5			
			Falling edge		5		μs	
t _{RESET}	Reset time	PB input held low	TRST = 0		8			
			TRST = 1		15		S	
V _{IH}	High level input voltage	SCL, SDA, GPIO1, GPIO3		1.3				
		AC_DET, PB		0.66*IN_ BIAS			V	
		PWR_EN		1.3				
V _{IL}	Low level input voltage	SCL, SDA, PWR_EN, AC_DE	T, PB, GPIO1, GPIO3	0		0.4	V	
V _{OH}	High level output voltage	utput voltage GPO2; I _{SOURCE} = 5 mA; GPO2_CNF=1		V _{IN_LS1} - 0.3		V _{IN_LS}		
		PGOOD_BU; I _{SOURCE} = 100 µ	ΙA	(VDD_18 - 10 mV)			V	
Col Low level output voltage		nPFO, nWAKEUP, nINT, SDA, PGOOD, GPIO1, GPO2, GPIO3; I _{SINK} = 2 mA		0		0.3	V	
		PGOOD_BU; I _{SINK} = 100 μA		0		0.3		
V_{PFI}	Power-fail comparator threshold	Input falling			800		.,	
	Hysteresis	Input rising			40		mV	
	Accuracy			-4%		4%		
	Deglitch	Input falling			25		μs	
		Input rising			10		ms	
I _{DC34_SEL}	DC34_SEL bias current	Enabled only at power-up			10		μΑ	
V _{DC34_SEL}	DCDC3 / DCDC4 power-up	Threshold1			100			
	default selection thresholds	Threshold2			163			
		Threshold3			275			
		Threshold4			400		mV	
		Threshold5			575			
		Threshold6			825			
		Threshold7			1200			
R _{DC34_SEL}	DCDC3 / DCDC4 power-up	Setting 0		0	0	7.7		
	default selection resistor values	Setting 1		11.3	12.1	13.0		
		Setting 2		18.1	20.0	22.0		
		Setting 2 Setting 3		30.9	31.6	32.3		
		Setting 4		44.8	45.3	46.4	kΩ	
		Setting 5		64.2	64.9	66.3		
		Setting 6		92.9	95.3	96.9		
		Setting 7		135.3	150			

Electrical Characteristics (continued)

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _{BIAS} Input bias current		SCL, SDA, GPIO1 ⁽⁶⁾ , GPIO3 ⁽⁶⁾ ; V _{IN} = 3.3 V		0.01	1.0	μA
		PB, AC_DET, PFI; V _{IN} = 3.3 V			500	nA
I _{LEAK} Pin leakage current		$\begin{array}{cccccccccccccccccccccccccccccccccccc$			500	nA
		V _{OUT} = 3.3 V				
OSCILLA	ATOR					
f_{OSC}	Oscillator frequency			2400		KHz
	Frequency accuracy	$T_{J} = -40 \text{ to } 105\text{C}$	-12%		12%	
OVER T	EMPERATURE SHUTDOWN					
T _{OTS}	Over temperature shutdown	Increasing junction temperature	135	145	155	°C
Hysteresis Decreasing junction		Decreasing junction temperature		20		٠.
T _{WARN}	High-temperature warning	Increasing junction temperature	90	100	110	°C
	Hysteresis	Decreasing junction temperature		15		3C

- (6) Configured as input.(7) Configured as output.(8) Configured as open-drain output.

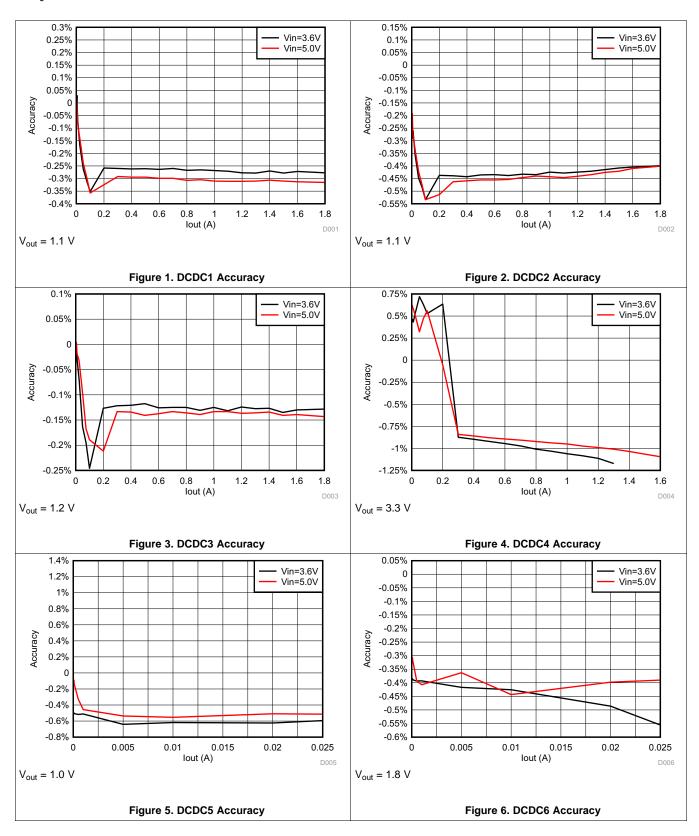
7.6 Timing Requirements

PARAM	ETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
f _{SCL}	Serial clock frequency				100 400	KHz
t _{HD;STA}	Hold time (repeated) START condition. After this period, the first clock pulse is generated.	SCL = 100 KHz SCL = 400 KHz	4.0 600			μs ns
t _{LOW}	LOW period of the SCL clock	SCL = 100 KHz SCL = 400 KHz	4.7 1.3			μs μs
t _{HIGH}	HIGH period of the SCL clock	SCL = 100 KHz SCL = 400 KHz	4.0 1.0			µs µs
t _{SU;STA}	Set-up time for a repeated START condition	SCL = 100 KHz SCL = 400 KHz	4.7 600			μs ns
t _{HD;DAT}	Data hold time	SCL = 100 KHz SCL = 400 KHz	0		3.45 900	μs ns
t _{SU;DAT}	Data set-up time	SCL = 100 KHz SCL = 400 KHz	250 100			ns ns
t _r	Rise time of both SDA and SCL signals	SCL = 100 KHz SCL = 400 KHz			1000 300	ns ns
t _f	Fall time of both SDA and SCL signals	SCL = 100 KHz SCL = 400 KHz			300 300	ns ns
t _{SU;STO}	Set-up time for STOP condition	SCL = 100 KHz SCL = 400 KHz	4.0 600			μs ns
t _{BUF}	Bus free time between Stop and Start condition	SCL = 100 KHz SCL = 400 KHz	4.7 1.3			µs µs
t _{SP}	Pulse width of spikes which mst be suppressed by the input filter	SCL = 100 KHz SCL = 400 KHz	n/a 0		n/a 50	ns
C _b	Capacitive load for each bus line	SCL = 100 KHz SCL = 400 KHz			400 400	pF

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7.7 Typical Characteristics

At T_J=25°C unless otherwise noted





8 Detailed Description

8.1 Overview

The TPS65218 provides three step-down converters, three load switches, three general purpose I/O's, two battery backup supplies, one Buck-Boost converter and one LDO. The system can be supplied by a single cell Li-lon battery or regulated 5-V supply. A coin-cell battery can be added to supply the two always-on backup supplies. The device is characterized across a -40°C to 105°C temperature range, which makes it suitable for various industrial applications.

The I²C interface provides comprehensive features for using TPS65218. All rails, Load-Switches and GPIOs can be enabled / disabled. Voltage thresholds for the UVLO and Supervisor can be customized. Power-up and power-down sequences can also be programmed through I²C. Interrupts for over-temperature, over-current and under-voltage can be monitored as well.

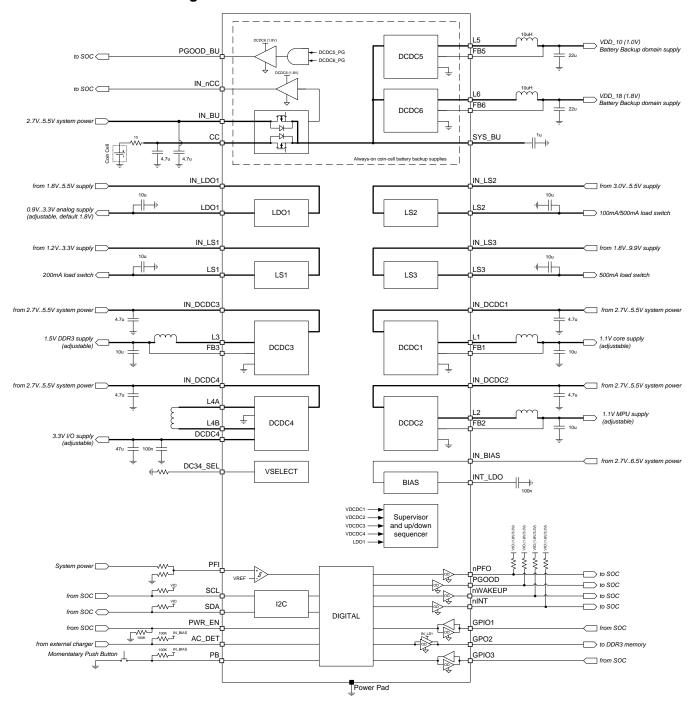
The integrated voltage supervisor monitors DCDC 1-4 & LDO1. It has two settings; the standard settings only monitors for under-voltage, while the strict settings implements tight tolerances on both under-voltage and overvoltage. A power good signal is provided to report the regulation state of the five rails.

The three hysteretic step-down converters can each supply up to 1.8A of current. The default output voltages for each converter can be adjusted through the I2C interface. DCDC 1 & 2 feature dynamic voltage scaling with adjustable slew rate. The step-down converters operate in a low power mode at light load, and can be forced into PWM operation for noise sensitive applications.

The battery backup supplies consist of 2 low power step-down converters optimized for very light loads and are monitored with a separate power good signal. The converters can be configured to operate as always-on supplies with the addition of a coin cell battery. The battery's state can be monitored over I²C.

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8.2 Functional Block Diagram

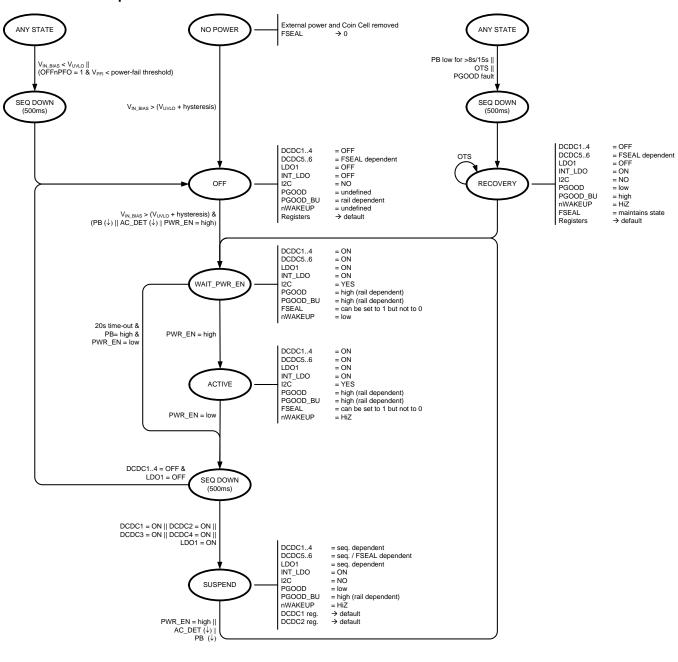


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8.3 Feature Description

8.3.1 Modes of Operation



NOTES:

PB (\$\partial\$) has 50ms debounce

AC_DET (\$\partial\$) has 10 ms debounce

Figure 7. Modes of Operation

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Feature Description (continued)

8.3.2 Wake-Up and Power Up and Power--Down Sequencing

The TPS65218 has a pre-defined power-up and power-down sequence, which in a typical application does not need to be changed. The user defines custom sequences under I2C control. The power-up sequence is defined by a series of ten strobes and nine delay times. Each output rail is assigned to a strobe to determine the order of enabling rails. A single rail is assigned to only one strobe, but multiple rails can be assigned to the same strobe. The delay times between strobes are between 2 and 5 ms.

8.3.2.1 Power-up Sequencing

When the power-up sequence initiates, STROBE1 occurs, and any rail assigned to this strobe is enabled. After a delay time of DLY1, STROBE2 occurs and the rail assigned to this strobe is powered up. The sequence continues until all strobes occur and all DLYx times execute. Strobe assignments and delay times are defined in the SEQx registers, and are changed under I2C control. The power up sequence executes if one of the following events occurs:

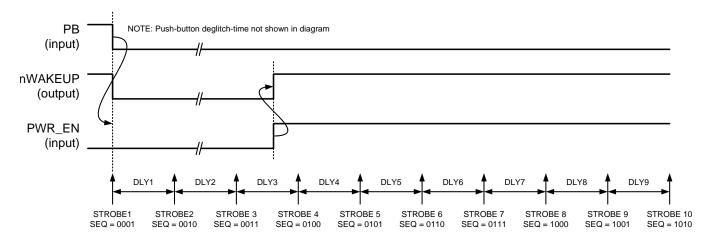
- · From the OFF state:
 - The push-button is pressed (falling edge on PB) OR
 - The AC_DET pin is pulled low OR
 - The PWR EN is asserted (driven to high-level) OR
 - The main power is connected (IN_BIAS) and AC_DET is grounded AND
 - The device is not in Under Voltage Lockout (UVLO) or Over Temperature Shutdown (OTS).
- From the SUSPEND state:
 - The push-button is pressed (falling edge on PB_IN) OR
 - The AC DET pin is pulled low (falling edge) OR
 - The PWR EN pin is pulled high (level sensitive) AND
 - The device is not in Under Voltage Lockout (UVLO) or Over Temperature Shutdown (OTS).

When a power-up event is detected, the device enters a WAIT_PWR_EN state and triggers the power-up sequence. The device remains in WAIT_PWR_EN as long as the PWR_EN and either the PB or AC_DET pin are held low. If both, the PB and AC_DET return to logic-high state and the PWR_EN pin has not been asserted within 20s of entering WAIT_PWR_EN state, the power-down sequence is triggered and the device returns to OFF state. Once PWR_EN is asserted, the device advances to ACTIVE state, which is functionally equivalent to WAIT_PWR_EN. However, the AC_DET pin is ignored and power-down is controlled by the PWR_EN pin only.

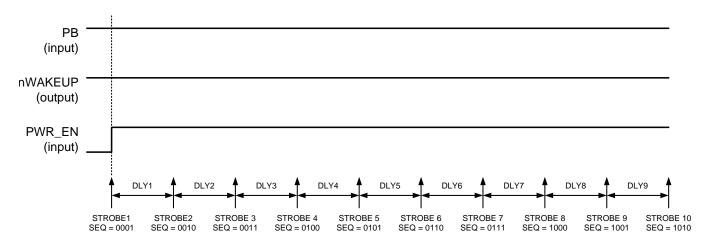
Rails not assigned to a strobe (SEQ=0000b) are not affected by power-up and power-down sequencing and remain in their current ON/OFF state regardless of the sequencer. A rail can be enabled/disabled at any time by setting the corresponding enable bit in the ENABLE register, with the exception that the ENABLE register cannot be accessed while the sequencer is active. Enable bits always reflect the current enable state of the rail, for example the sequencer sets and resets the enable bits for the rails under its control.

Feature Description (continued)

Power-up from OFF or SUSPEND state; PB is power-up event.



Power-up from SUSPEND state; PWR_EN is power-up event.



Power-up from RECOVERY state

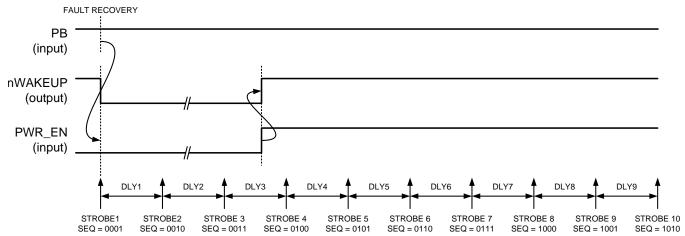


Figure 8. Power-Up Sequences from Different States

NSTRUMENTS

Feature Description (continued)

Note: The power-up sequence is defined by strobes and delay times, and can be triggered by the PB, AC_DET (not shown, same as PB), or PWR_EN pin.

8.3.2.2 Power-down Sequencing

By default, the power-down sequence follows the reverse of the power-up sequence. When the power-down sequence is triggered, STROBE10 occurs and any rail assigned to STROBE10 is shut down and its discharge circuit is enabled. After a delay time of DLY9, STROBE9 occurs and any rail assigned to it is shut down and its discharge circuit enabled. The sequence continues until all strobes occur and all DLYx times execute. The DLYx times are extended by a factor of 10x to provide ample time for discharge, and preventing output voltages from crossing during shut-down. The DLFCTR bit is applied globally to all power-down delay times. Regardless of the DLYx and DLFCTR settings, the PMIC enters OFF, SUSPEND, or RECOVERY state 500 ms after the powerdown sequence initiates, to ensure that the discharge circuits remain enabled for a minimum of 50 ms before the next power-up sequence starts.

A power-down sequence executes if one of the following events occurs:

- The device is in the WAIT PWR EN state, the PB and AC DET pins are high, PWR EN is low, and the 5s timer has expired.
- The device is in the ACTIVE state and the PWR_EN pin is pulled low.
- The device is in the WAIT PWR EN, ACTIVE, or SUSPEND state and the push-button is pressed for >8s (15s if TRST=1)
- A fault occurs in the IC (OTS, UVLO, PGOOD failure).

When transitioning from ACTIVE to SUSPEND state, rails not controlled by the power-down sequencer maintains the same ON/OFF state in SUSPEND state that it had in ACTIVE state. This allows keeping selected power rails up in SUSPEND.

When transitioning to the OFF or RECOVERY state, rails not under sequencer control are shut-down as follows:

- DCDC1, 2, 3, 4, LDO1, and LS1 shut down at the beginning of the power-down sequence, if not under sequencer control (SEQ=0).
- LS2 and LS3 shut down as the state machine enters an OFF or RECOVERY state; 500 ms after the powerdown sequence is triggered.

8.3.2.3 Strobes 1 and 2

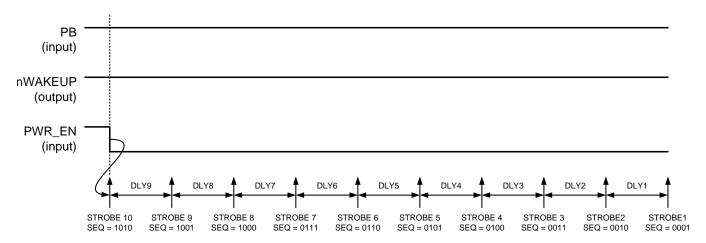
STROBE1 and STROBE2 are dedicated to DCDC5 and DCDC6 which are 'always-on'; powered up as soon as the device exits the OFF state, and ON in any other state. STROBE 1 and 2 options are available only for DCDC5 and DCDC6, not for any other rails.

STROBE 1 and STROBE 2 occur in every power-up sequence, regardless if the rail is already powered up. If the rail is not to be powered up, its respective strobe setting must be set to 0x00.

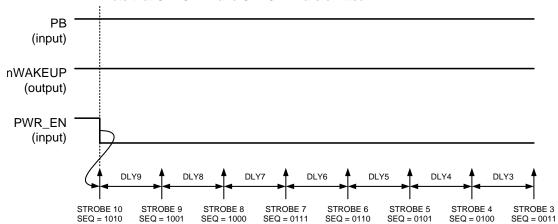
When a power-down sequence initiates, STROBE1 and STROBE2 occur only if the FSEAL bit is 0. Otherwise, both strobes are omitted and DCDC5 and DCDC6 maintain state.

Feature Description (continued)

Power-down to OFF state. PWR_EN is power-down event. FSEAL = 0.



Power-down to SUSPEND state. PWR_EN is power-down event. FSEAL = 1. Note that STROBE2 and STROBE1 are omitted.



Power-down to RECOVERY state. TSD or UV is power-down event. FSEAL = 1. Note that STROBE2 and STROBE1 are omitted.

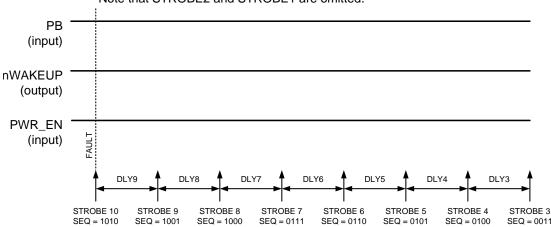


Figure 9. Power-Down Sequences to Different States

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Feature Description (continued)

Note: The power-down sequence follows the reverse of the power-up sequence. STROBE2 and STROBE1 are executed only if FSEAL bit is 0.

8.3.2.4 Supply Voltage Supervisor And Power Good (PGOOD)

Power-good (PGOOD) is an open-drain output of the built-in voltage supervisor that monitors DCDC1, DCDC2, DCDC3, DCDC4, and LDO1. The output is HiZ when all enabled rails are in regulation and driven low when one or more rails encounter a fault which brings the output voltage outside the specified tolerance range. In a typical application PGOOD drives the reset signal of the SOC.

The supervisor has two modes of operation, controlled by the STRICT bit. With the STRICT bit set to 0, all five rails are monitored for under-voltage only with relaxed thresholds and deglitch times. With the STRCT bit set to 1, all five rails are monitored for under-voltage and over-voltage with tight limits and short deglitch times. Table 1 summarizes these details.

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	PARAMETER	STRICT = 0	STRICT = 1
Undervoltage monitoring	Threshold (output falling)	90%	96.5% (DCDC1, DCDC2) 95.5% (DCDC3, DCDC4)
Ondervoltage monitoring	Deglitch (output falling)	1 ms	50 µs
	Deglitch (output rising)	10 us	10 us
Overvoltage monitoring	Threshold (output falling)	N/A	103.5% (DCDC1, DCDC2) 104.5% (DCDC3, DCDC4)
Overvoitage monitoring	Deglitch (output falling)	N/A	1 ms
	Deglitch (output rising)	N/A	50 µs

Table 1. Supervisor Characteristics Controlled by the STRICT Bit

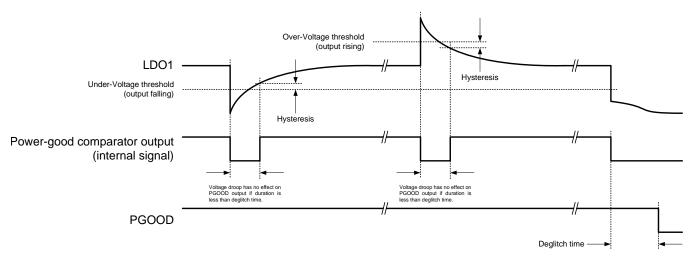


Figure 10. Definition of Under-voltage, Over-voltage Thresholds, Hysteresis and Deglitch Times

The following rules apply to the PGOOD output:

- The power-up default state for PGOOD is low. When all rails are disabled, PGOOD output is driven low.
- Only enabled rails are monitored. Disabled rails are ignored.
- Power-good monitoring of a particular rail starts 5 ms after the rail is enabled and is continuously monitored thereafter. This allows the rail to power-up.
- PGOOD is delayed by PGDLY time after the sequencer is finished and the last rail is enabled.
- If an enabled rail is continuously outside the monitoring threshold for longer than the deglitch time, PGOOD is pulled low, and all rails are shut-down following the power-down sequence. PGDLY does not apply.
- Disabling a rail manually by resetting the DCx_EN or LDO1_EN bit has no effect on the PGOOD pin. If all rails are disabled, PGOOD is driven low as the last rail is disabled.
- If the power-down sequencer is triggered, PGOOD is driven low together with the disabling of the first power rail.
- PGOOD is driven low in SUSPEND state, regardless of the number of rails that are enabled.

A typical power-up sequence and PGOOD timing are shown in Figure 11.

8.3.2.5 Backup Supply Power-good (PGOOD_BU)

PGOOD_BU is a push-pull output indicating if DCDC5 and DCDC6 are in regulation. The output is driven to high when both rails are in regulation, and driven low if at least one of the rails is below the power-good threshold. The output-high level is equal to the output voltage of DCDC6.

PGOOD_BU is the logical AND between PGOOD(DCDC5) and PGOOD(DCDC6), and has no delay time built-in. Unlike main power-good, a fault on DCDC5 or DCDC6 does not trigger the power-down sequencer, does not disable any of the rails in the system, and has no effect on the PGOOD pin. DCDC5 and DCDC6 recover automatically once the fault is removed.

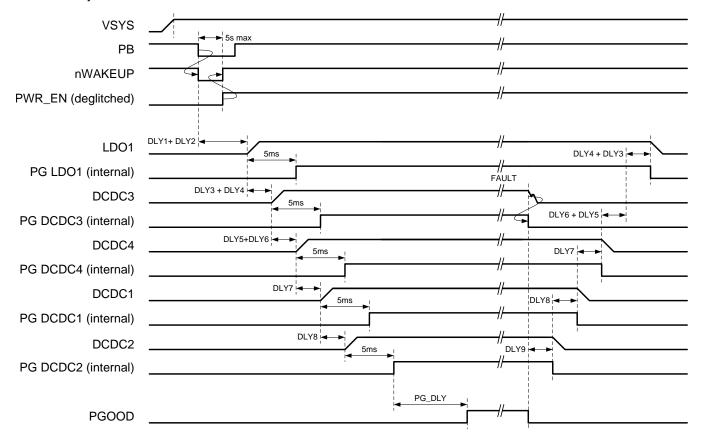


Figure 11. Typical Power-up Sequence of the Main Output Rails.

Note: In this example, the power-down is triggered by a fault on DCDC3.



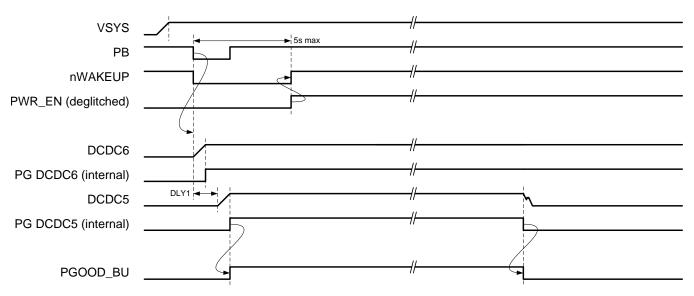


Figure 12. Typical Power-up Sequence of DCDC5 and DCDC6

8.3.2.6 Internal LDO (INT_LDO)

Internal LDO provides a regulated voltage to the internal digital core and analog circuitry. Internal LDO has a nominal output voltage of 2.5 V and can support up to 10 mA of external load.

When system power fails, the UVLO comparator triggers the power-down sequence. If system power drops below 2.5 V, the digital core is reset and all remaining power rails are shut down instantaneously.

The internal LDO reverse-blocks to prevent the discharge of the output capacitor, and the remaining charge on the INT_LDO output capacitor provides a supply for the power-rail discharge circuitry to ensure the outputs are discharged to ground even if the system supply has failed. The amount of hold-up time is a function of the output capacitor value, which should not exceed 22 uF and the amount of external load, if any.

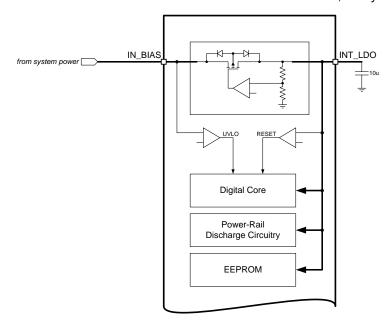


Figure 13. Internal LDO and Under-voltage Lockout Sensing

8.3.2.7 Current Limited Load Switches

The TPS65218 provides three current limited load switches with individual inputs, outputs, and enable control. Each switch provides the following control and diagnostic features:

- The ON/OFF state of the switch is controlled by the corresponding LSx_EN bit in the ENABLE register.
- Each switch has an active discharge function, disabled by default, and enabled through the LSxDCHRG bit. When enabled, the switch output is discharged to ground whenever the switch is disabled.
- When the PFI input drops below the power-fail threshold (the power-fail comparator trips), the load switches
 are automatically disabled to shed system load. This function must be individually enabled for each switch
 through the corresponding LSxnPFO bit. The switches do not turn back on automatically as the system
 voltage recovers, and must be manually re-enabled.
- An interrupt (LSx_I) issues whenever a load switch actively limits the output current, such as when the output load exceeds the current limit value. The switch remains ON and provides current to the load according the current-limit setting.
- All three load switches have local over-temperature sensors which disable the corresponding switch if the
 power dissipation and junction temperature exceeds safe operating value. The switch automatically recovers
 once the temperature drops below the OTS threshold value. The LSx_F (fault) interrupt bit is set while the
 switch is held OFF by the OTS function.

8.3.2.7.1 Load switch 1 (LS1)

LS1 is a non-reverse blocking, low-voltage (<3.3 V), low-impedance switch intended to support DDR3 self-refresh mode by cutting off the DDR3 supply to the SOC DDR3 interface during SUSPEND mode. In a typical application, the input of LS1 is tied to the output of DCDC3 and the output connected to the memory-interface supply pin of the SOC. LS1 can be controlled by the internal sequencer, just as any power rail.

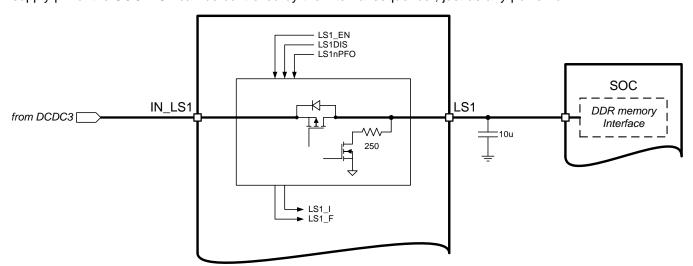


Figure 14. Typical Application of Load Switch 1

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8.3.2.7.2 Load Switch 2 (LS2)

LS2 is a reverse-blocking, 5 V, low-impedance switch. Load switch 2 provides four different current limit values (100/200/500/1000 mA) that are selectable through LS2ILIM[1:0] bits. Over-current is reported through the LS2_I interrupt.

LS2 has its own input-under-voltage protection which forces the switch OFF if the switch input voltage (V_{IN_LS2}) is <2.7 V. Similar to OTS, the LS2_F interrupt is set when the switch is held OFF by the local UVLO function, and the switch recovers automatically when the input voltage rises above the UVLO threshold.

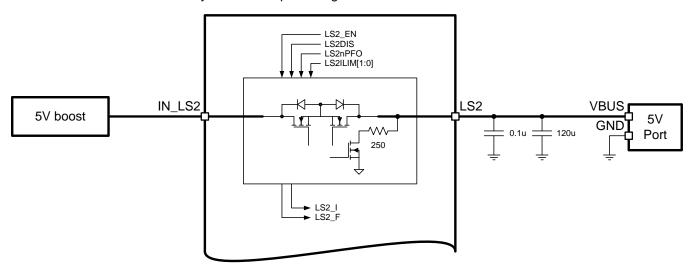


Figure 15. Typical Application of Load Switch 2

8.3.2.7.3 Load Switch 3 (LS3)

LS3 is a non-reverse blocking, medium-voltage (<10 V), low-impedance switch that can be used to provide 1.8..9 V power to an auxiliary port. LS3 has four selectable current limit values in the range of 100 mA to 1 A.

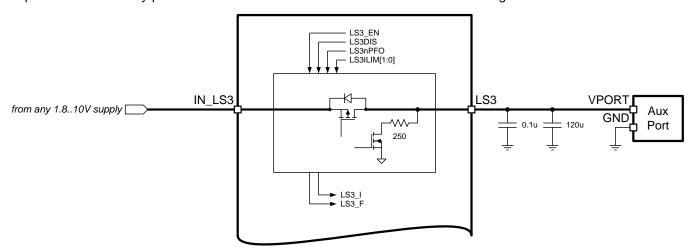


Figure 16. Typical Application of Load Switch 3

8.3.2.8 LDO1

LDO1 is a general-purpose LDO intended to provide power to analog circuitry on the SOC. LDO1 has an input voltage range from 1.8 V to 5.5 V, and can be connected either directly to the system power or the output of a DCDC converter. The output voltage is programmable in the range of 0.9 V to 3.4 V with a default of 1.8 V. LDO1 supports up to 200 mA at the minimum specified head-room voltage, and up to 400 mA at the typical operating condition of V_{OUT} =1.8 V, $V_{IN\ LDO1}$ >2.7 V.

8.3.2.9 Coin Cell Battery Voltage Acquisition

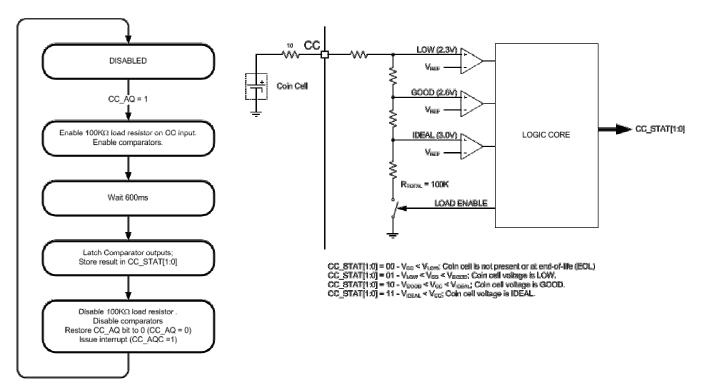


Figure 17. Left: Flow Chart for Acquiring Coin Cell Battery Voltage. Right: Comparator Circuit

8.3.2.10 Under Voltage Lock Out (UVLO)

Power rails are only enabled if the input voltage measured at the IN_BIAS pin is greater than the under-voltage lockout threshold plus hysteresis ($V_{UVLO} + V_{HYS}$). Once the input voltage rises above this level, the input voltage may drop to the UVLO level before the PMIC shuts down. UVLO is deglitched by 5 ms on rising and falling edge.

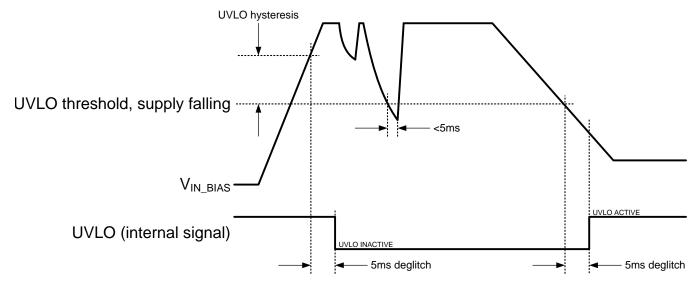


Figure 18. Definition of Under Voltage Lockout and Hysteresis



Once the UVLO triggers, the internal LDO blocks current flow from its output capacitor back to the IN_BIAS pin, allowing the digital core and the discharge circuits to remain powered for a limited amount of time to properly shut-down and discharge the output rails. The hold-up time is determined by the size of the capacitor connected to INT_LDO. See Internal LDO (INT_LDO) for more details.

8.3.2.11 Power-fail Comparator

The power-fail comparator notifies the system host if the system supply voltage drops and the system is at risk of shutting down. The comparator has an internal 800 mV threshold and the trip-point is adjusted by an external resistor divider.

By default, the power-fail comparator has no impact on any of the power rails or load switches. Load switches are configured individually, to be disabled when the PFI comparator trips to shed system load and extend hold-up time as described under Current Limited Load Switches. The power-fail comparator also triggers the power-down sequencer, such that all or selective rails power down when the system voltage fails. To tie the power-fail comparator into the power-down sequence, the OFFnPFO bit in the CONTROL register must be set to 1.

The power-fail comparator cannot be monitored by software, such that no interrupt or status bit is associated to this function.

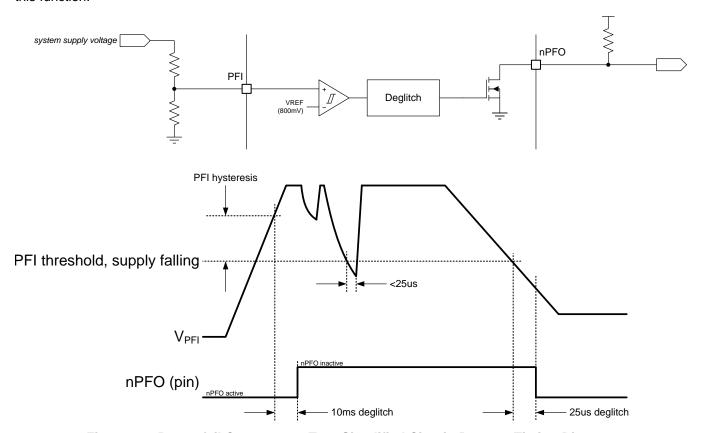


Figure 19. Power-fail Comparator. Top: Simplified Circuit. Bottom: Timing Diagram

8.3.2.12 Battery-backup Supply Power-path

DCDC5 and DCDC6 are supplied from either the CC (coin-cell battery) input or IN_BU (main system supply). The power-path is designed to prioritize IN_BU to maximize coin-cell battery life. Whenever the PMIC is powered-up (WAIT_PWR_EN, ACTIVE, SUSPEND, RECOVERY state), the power-path is forced to select the IN_BU input. In OFF mode the power-path selects the higher of the two inputs with a built-in hysteresis of 150 mV as shown in Figure 20A.

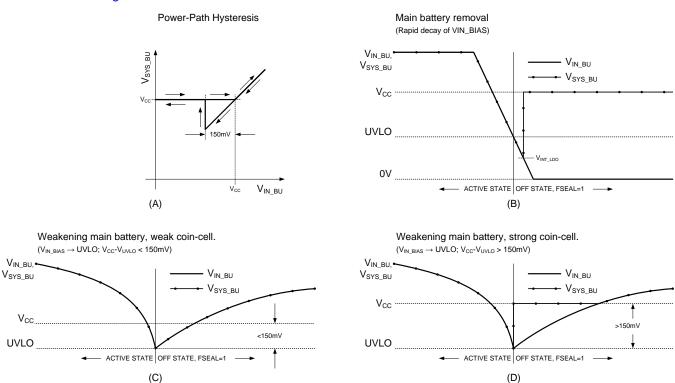


Figure 20. Switching behavior of the Battery-Backup-Supply Power-Path.

Image key: (A) Power-path Hysteresis. (B) Main Supply is disconnected or decays rapidly. (C) System is supplied by Li-lon battery with a weak coin-cell backup battery. (D) System is supplied by Li-lon battery with a fresh coin-cell backup battery.

When V_{IN_BIAS} drops below the UVLO threshold, the PMIC shuts down all rails and enters OFF mode. At this point the power-path selects the higher of the two input supplies. If the coin-cell battery is less than 150 mV above the UVLO threshold, SYS_BU remains connected to IN_BU. This is shown in Figure 20C. If the coin-cell is >150 mV above the UVLO threshold, the power-path switches to the CC input as shown in Figure 20D. With no load on the main supply, the input voltage may recover over time to a value greater than the coin-cell voltage and the power-path switches back to IN_BU. This is a typical behavior in a Li-Ion battery powered system.

Depending on the system load, V_{IN_BIAS} may drop below VI_{NT_LDO} before the power-down sequence is completed. In that case, INT_LDO is turned OFF and the digital core is reset forcing the unit into OFF mode and the power-path switches to IN BU as shown in Figure 20B.

8.3.2.12.1 Applications without Backup Battery

In applications that require always-on supplies but no battery backup, the CC input to the power path must be connected to ground.



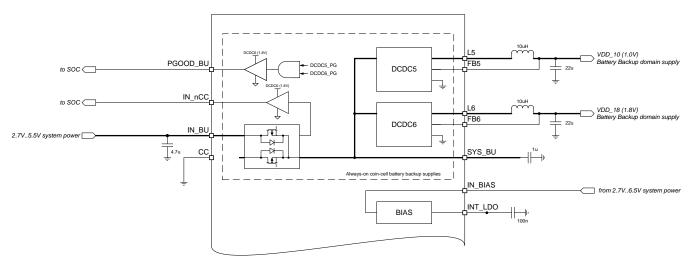


Figure 21. CC Input to Power Path

Note: In applications without backup battery, CC input must be tied to ground.

8.3.2.12.2 Applications Without Battery Backup Supplies

In applications that do not require always-on supplies, both inputs and the output of the power-path can simply be grounded. All pins related to DCDC5 and DCDC6 are also tied to ground, and PGOOD_BU and IN_nCC are kept floating. With the backup supplies completely disabled, the FSEAL bit in the STATUS register is undefined and should be ignored.

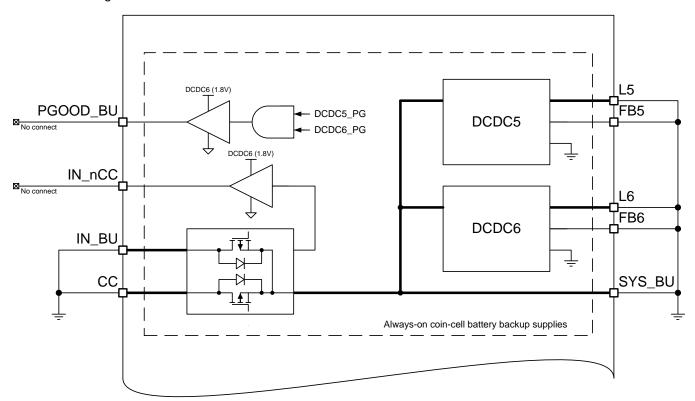


Figure 22. DCDC5 and DCDC6 Pins

Note: In applications that do not require always-on supplies, PGOOD_BU and IN_nCC can be kept floating. All other pins are tied to ground.

8.3.2.13 DCDC3 / DCDC4 Power-up Default Selection

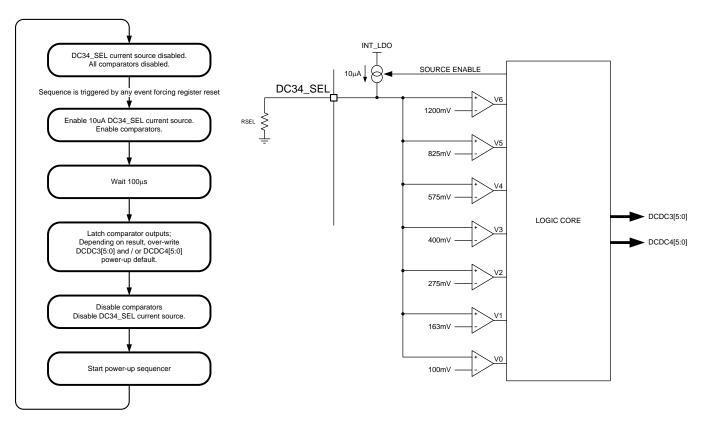


Figure 23. Left: Flow Chart for Selecting DCDC Power-up Default Voltage. Right: Comparator Circuit

POWER-UP DEFAULT RSEL [KΩ] MIN **TYP** MAX DCDC3[5:0] DCDC4[5:0] 0 0 7.7 Programmed default (1.2 V) Programmed default (3.3 V) 0x12 (1.35 V) Programmed default (3.3 V) 11.3 12.1 13.0 18.1 20.0 22.0 0x18 (1.50 V) Programmed default (3.3 V) 32.3 0x1F (1.80 V) Programmed default (3.3 V) 30.9 31.6 44.8 45.3 46.4 0x3D (3.30 V) 0x01 (1.20 V) Programmed default (1.2 V) 0x07 (1.35 V) 64.2 64.9 66.3 92.9 95.3 96.9 Programmed default (1.2 V) 0x0D (1.50 V) Tied to 135.3 150 Programmed default (1.2 V) 0x14 (1.80 V) INT LDO

Table 2. Power-up Default Values of DCDC3 and DCDC4

8.3.2.14 I/O Configuration

The device has two GPIOs and one GPO pin which are configured as follows:

- GPIO1:
 - General-purpose, open-drain output controlled by GPO1 user bit or sequencer
 - DDR3 reset input signal from SOC. Signal is either latched or passed-trough to GPO2 pin. See Table 3 for details.
- GPO2:
 - General-purpose output controlled by GPO2 user bit
 - DDR3 reset output signal. Signal is controlled by GPIO1 and PGOOD. See Table 4 for details.
 - Output buffer is configured as open-drain or push-pull.



- GPIO3:
 - General-purpose, open-drain output controlled by GPO3 user bit or sequencer
 - Reset input-signal for DCDC1 and DCDC2

Table 3. GPIO1 Configuration

IO1_SEL (EEPROM)	GPO1 (USER BIT)	PGOOD (PMIC SIGNAL)	GPIO1 (I/O PIN)	COMMENTS
0	0	X	0	Open-drain output, driving low
0	1	X	HiZ	Open-drain output, HiZ
1	Х	0	Х	Pin is configured as input and intended as DDR RESET signal. Coming out of POR, GPO2 is driven low. Otherwise, GPO2 status is latched at falling edge of PGOOD. See Figure 26.
1	Х	1	0	Pin is configured as input and intended as DDR RESET signal. GPO2 is driven low.
1	Х	1	1	Pin is configured as input and intended as DDR RESET signal. GPO2 is driven high.

Table 4. GPO2 Configuration

IO1_SEL (EEPROM)	GPO2_BUF (EEPROM)	GPO2 (USER BIT)	COMMENTS
0	0	0	GPO2 is open drain output controlled by GPO2 user bit (driving low).
0	0	1	GPO2 is open drain output controlled by GPO2 user bit (HiZ).
0	1	0	GPO2 is push-pull output controlled by GPO2 user bit (driving low).
0	1	1	GPO2 is push-pull output controlled by GPO2 user bit (driving high).
1	0	X	GPO2 is open drain output controlled by GPIO1/PGOOD.
1	1	X	GPO2 is push-pull output controlled by GPIO1/PGOOD.

Table 5. GPO3 Configuration

DC12_RST (EEPROM)	GPO3 (USER BIT)	GPIO3 (I/O PIN)	COMMENTS
0	0	0	Open-drain output, driving low
0	1	HiZ	Open-drain output, HiZ
1	X	Active low	GPIO3 is DCDC1 and DCDC2 reset input signal to PMIC (active low). See Using GPIO3 as Reset Signal to DCDC1 and DCDC2 for details.

8.3.2.14.1 Configuring GPO2 as Open-Drain Output

GPO2 may be configured as open-drain or push-pull output. The supply for the push-pull driver is internally connected to the IN_LS1 input pin, whereas an external pull up resistor and supply are required in the open-drain configuration. Because of the internal connection to IN_LS1, the external pull-up supply must not exceed the voltage on the IN_LS1 pin, otherwise leakage current may be observed from GPO2 to IN_LS1 as shown in Figure 24.

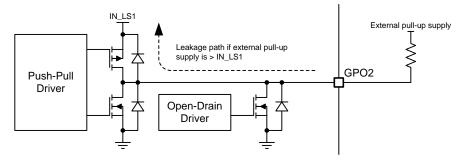


Figure 24. GPO2 as Open-Drain Output

Note: When configured as open-drain output, the external pull-up supply must not exceed the voltage level on IN_LS1 pin.

8.3.2.14.2 Using GPIO3 as Reset Signal to DCDC1 and DCDC2

With the DC12_RST bit set to 1, GPIO3 is an edge-sensitive reset input to the PMIC. The reset signal affects DCDC1 and DCDC2 only, so that only those two registers are reset to the power-up default whenever GPIO3 input transitions from high to low, while all other registers maintain their current values. DCDC1 and DCDC2 transition back to the default value following the SLEW settings, and are not power cycled. This function recovers the processor from reset events while in low-power mode.

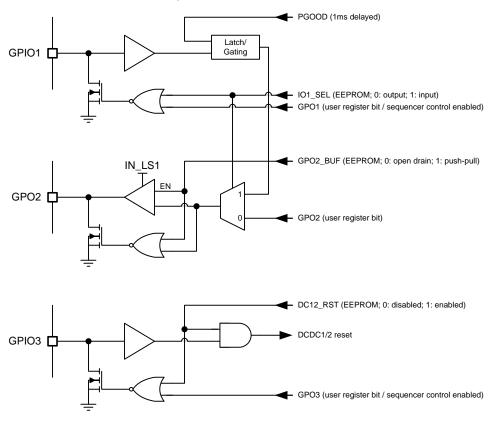


Figure 25. I/O Pin Logic

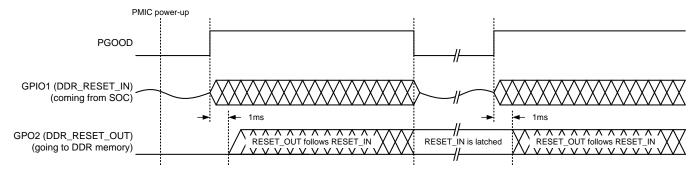


Figure 26. DDR3 Reset Timing Diagram.

Note: GPIO must be configured as input (IO1_SEL=1). GPO2 is automatically configured as output.

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8.3.2.15 Push Button Input (PB)

The PB pin is a CMOS-type input used to power-up the PMIC. Typically, the PB pin is connected to a momentary switch to ground and an external pull-up resistor. The power-up sequence is triggered if the PB input is held low for 600ms.

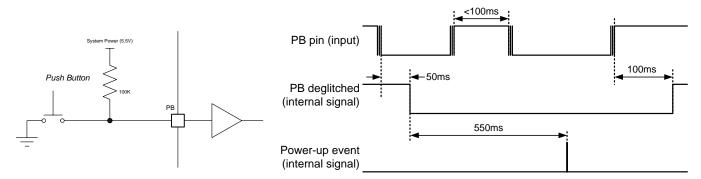


Figure 27. Left: Typical PB Input Circuit. Right: Push-button Input (PB) Deglitch and Power-up Timing

In ACTIVE mode, the TPS65218 monitors the PB input and issues an interrupt when the pin status changes, such as when it drops below or rises above the PB input-low or input-high thresholds. The interrupt is masked by the PBM bit in the INT_MASK1 register.

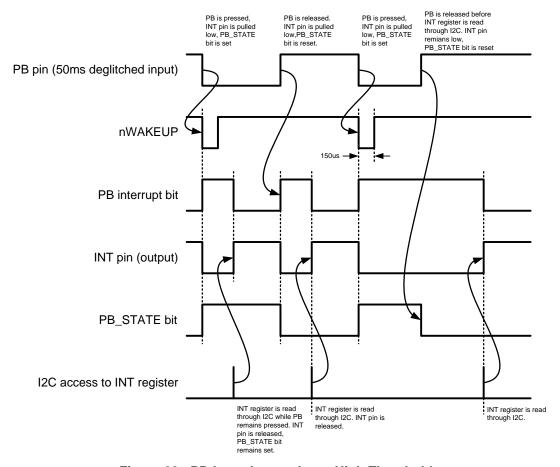


Figure 28. PB Input-Low or Input-High Thresholds

Note: Interrupts are issued whenever the PB pin status changes. The PB_STATE bit reflects the current status of the PB input. nWAKEUP is pulled low for 150 us on every falling edge of PB.

8.3.2.15.1 Signaling PB-low Event on the nWAKEUP Pin

In ACTIVE state, the nWAKEUP pin is pulled low for 5 32kHz clock cycles (approximately 150 us) whenever a falling edge on the PB input is detected. This allows the host processor to wakeup from DEEP SLEEP mode of operation.

8.3.2.15.2 Push Button Reset

If the PB input is pulled low for 8s (15s if TRST=1) or longer, all rails except for DCDC5 and DCDC6 are disabled, and the device enters the RECOVERY state. The device powers up automatically after the 500 ms power-down sequence is complete, regardless of the state of the PB input. Holding the PB pin low for 8s (15s if TRST=1), only turns off the device temporarily and forces a system restart, and is not a power-down function. If the PB is held low continuously, the device power-cycles in 8s and 15s intervals.

8.3.2.16 AC_DET Input (AC_DET)

The AC_DET pin is a CMOS-type input used in three different ways to control the power-up of the PMIC:

- In a battery operated system, AC_DET is typically connected to an external battery charger with an opendrain power-good output pulled low when a valid charger supply is connected to the system. A falling edge on the AC_DET pin causes the PMIC to power up.
- In a non-portable system, the AC_DET pin may be shorted to ground and the IC powers up whenever system power is applied to the chip.
- If none of the above behaviors are desired, AC_DET may be tied to system power (IN_BIAS). Power-up is then controlled through the push-button input only.

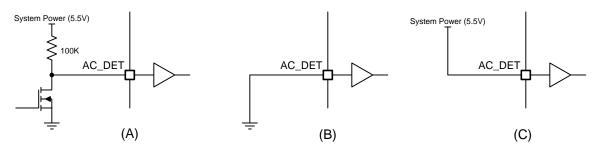


Figure 29. AC_DET Pin Configurations. (A) Portable Systems. (B) Non-portable Systems. (C) Disabled

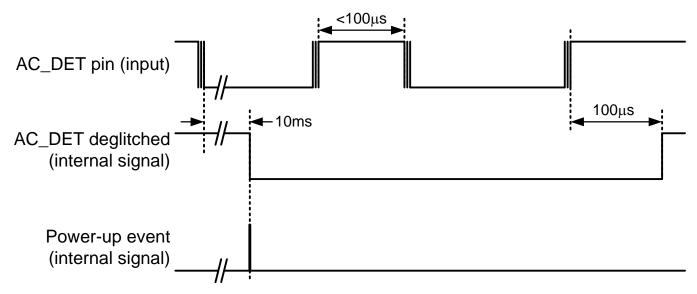


Figure 30. AC DET Input Deglitch and Power-up Timing (Portable Systems)



In ACTIVE state, the TPS65218 monitors the AC_DET input and issues an interrupt when the pin status changes, such as when it drops below or rises above the AC_DET input-low or input-high thresholds. The interrupt is masked by the ACM bit in the INT_MASK1 register.

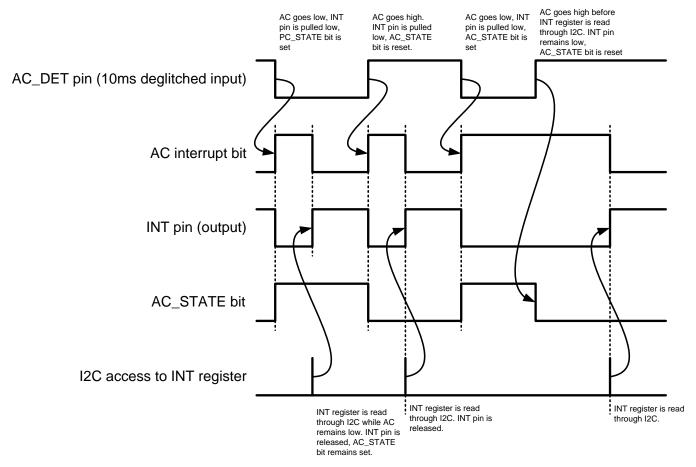


Figure 31. AC_STATE Pin

Note: Interrupts are issued whenever the AC_DET pin status changes. The AC_STATE bit reflects the current status of the AC_DET input.

8.3.2.17 Interrupt Pin (INT)

The interrupt pin signals any event or fault condition to the host processor. Whenever a fault or event occurs in the IC, the corresponding interrupt bit is set in the INT register, and the open-drain output is pulled low. The INT pin is released (returns to HiZ state) and fault bits are cleared when the host reads the INT register. If a failure persists, the corresponding INT bit remains set and the INT pin is pulled low again after a maximum of 32 us.

The MASK register masks events from generating interrupts. The MASK settings affect the INT pin only, and have no impact on the protection and monitor circuits.

8.3.2.18 I2C Bus Operation

The TPS65218 hosts a slave I2C interface (address 0x24) that supports data rates up to 400kbit/s, auto-increment addressing, and is compliant to I2C standard 3.0.



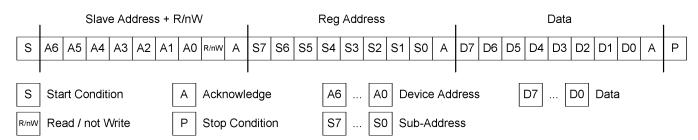


Figure 32. Sub-address in I²C Transmission

The I²C Bus is a communications link between a controller and a series of slave terminals. The link is established using a two-wired bus consisting of a serial clock signal (SCL) and a serial data signal (SDA). The serial clock is sourced from the controller in all cases where the serial data line is bi-directional for data communication between the controller and the slave terminals. Each device has an open drain output to transmit data on the serial data line. An external pull-up resistor must be placed on the serial data line to pull the drain output high during data transmission.

Data transmission initiates with a start bit from the controller as shown in Figure 34. The start condition is recognized when the SDA line transitions from high to low during the high portion of the SCL signal. Upon reception of a start bit, the device receives serial data on the SDA input and checks for valid address and control information. If the appropriate slave address is set for the device, the device issues an acknowledge pulse and prepares to receive register address and data. Data transmission is completed by either the reception of a stop condition or the reception of the data word sent to the device. A stop condition is recognized as a low to high transition of the SDA input during the high portion of the SCL signal. All other transitions of the SDA line must occur during the low portion of the SCL signal. An acknowledge issues after the reception of valid slave address, register-address, and data words. The I2C interfaces auto-sequence through register addresses, so that multiple data words can be sent for a given I2C transmission. Reference Figure 33 and Figure 34 for details.

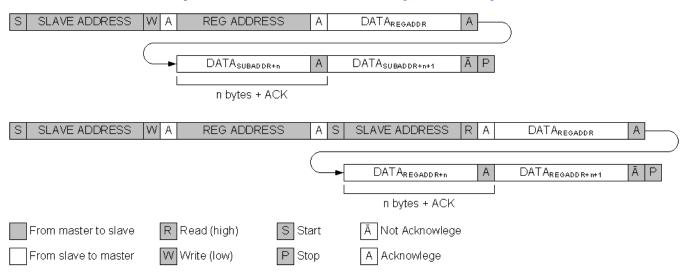
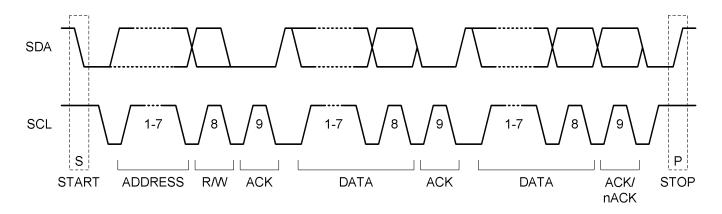


Figure 33. I²C Data Protocol. Top: Master Writes Data to Slave. Bottom: Master Reads Data from Slave



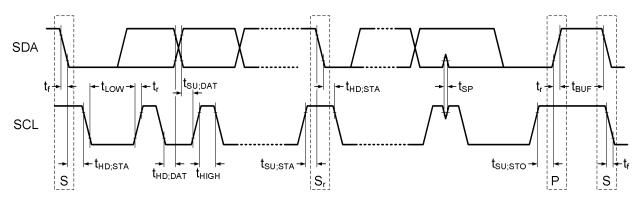


Figure 34. Top: I²C Start/Stop/Acknowledge Protocol. Bottom: I²C Data Transmission Timing

8.4 Device Functional Modes

8.4.1 OFF

In OFF mode, the PMIC is completely shut down with the exception of a few circuits to monitor the AC_DET, PWR_EN and PB input. All power rails are turned off and the registers are reset to their default values. The I^2C communication interface is turned off. This is the lowest-power mode of operation. To exit OFF mode V_{IN_BIAS} must exceed the UVLO threshold and one of the following wake-up events must occur:

- The PB input is pulled low.
- THE AC DET input is pulled low.
- The PWR_EN input is pulled high.

To enter OFF state, ensure all power rails are assigned to e sequencer, then pull the PWR_EN pin low. Additionally, if the OFFnPFO bit is set to 1 and the PFI input falls below the power fail threshold the device transitions to the OFF state. If the freshness seal is broken, DCDC5 and DCDC6 remains on in the OFF state.

If a PGOOD or OTS fault occurs while in the ACTIVE state, TPS65218 will transition to the RESET state.

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Device Functional Modes (continued)

8.4.2 ACTIVE

This is the typical mode of operation when the system is up and running. All DCDC converters, LDOs, and load switches are operational and can be controlled through the I²C interface. After a wake-up event, the PMIC enables all rails controlled by the sequencer and pulls the nWAKEUP pin low to signal the event to the host processor. The device only enters ACTIVE state if the host asserts the PWR_EN pin within 20 seconds after the wake-up event. Otherwise it will enter OFF state. The nWAKEUP pin returns to HiZ mode after the PWR_EN pin is asserted. ACTIVE state can also be directly entered from SUSPEND state by pulling the PWR_EN pin high. See SUSPEND state description for details. To exit ACTIVE mode, the PWR_EN pin must be pulled low.

8.4.3 SUSPEND

SUSPEND state is a low-power mode of operation intended to support system standby. Typically all power rails are turned off with the exception of any rail with an SEQ register set to 0h. DCDC5 and DCDC6 also remain enabled if the freshness seal is broken. To enter SUSPEND state, pull the PWR_EN pin low. All power rails controlled by the power-down sequencer are shut down, and after 500 ms the device enters SUSPEND state. All rails not controlled by the power-down sequencer will maintain state. Note that all register values are reset as the device enters the SUSPEND state. The device enters ACTIVE state after it detects a wake-up event as described in the sections above.

8.4.4 **RESET**

The TPS65218 can be reset by holding the PB pin low for more than 8 or 15 seconds, depending on the value of the TRST bit. All rails are shut-down by the sequencer and all register values reset to their default values. Rails not controlled by the sequencer are shut down additionally. Note that the RESET function power-cycles the device and only temporarily shuts down the output rails. Resetting the device does not lead to OFF state. If the PB_IN pin is kept low for an extended amount of time, the device continues to cycle between ACTIVE and RESET state, entering RESET every 8 or 15 s.

The device is also reset if a PGOOD or OTS fault occurs. The TPS65218 remains in the recovery state until the fault is removed, at which time it transitions back to the ACTIVE state.

8.5 Registers

8.5.1 Password Protection

Registers 0x11h through 0x26h are protected against accidental write by a 8-bit password. The password must be written prior to writing to a protected register and automatically resets to 0x00h after the next I2C transaction, regardless of the register accessed or transaction type (read or write). The password is required for write access only and is not required for read access.

To write to a protected register:

- 1. Write the address of the destination register, XORed with the protection password (0x7Dh), to the PASSWORD register (0x10h).
- 2. Write the data to the password protected register.
- 3. If the content of the PASSWORD register XORed with the address send matches 0x7Dh, the data transfers to the protected register. Otherwise, the transaction is ignored. In either case the PASSWORD register resets to 0x00 after the transaction.

The cycle must be repeated for any other register that is Level1 write protected.

8.5.2 The Freshness Seal (FSEAL) Bit

The FSEAL (freshness seal) bit prevents accidental shut-down of the always-on supplies, DCDC5 and DCDC6. The FSEAL bit exists in a default state of 0, and can be set to 1 and reset to 0 once for factory testing. The second time the bit is set to 1, it remains 1 and cannot reset again under software control. Coin-cell battery and main supply must be disconnected from the IC to reset the FSEAL bit again. With the FSEAL bit set to 1, DCDC5 and DCDC6 are forced ON regardless of the state of the DC5_EN and DC6_EN bit, and the rails do not turn off when the IC enters OFF mode.

TEXAS INSTRUMENTS

Registers (continued)

A consecutive write of [0xB1, 0xFE, 0xA3] to the password register sets the FSEAL bit to 1. The three bytes must be written consecutively for the sequence to be valid. No other read or write transactions are allowed between the three bytes, or the sequence is invalid. After a valid sequence, the FSEAL bit in the STATUS register reflects the new setting.

After setting the FSEAL bit, the IC can enter OFF or any other mode of operation without affecting the state of the FSEAL bit, provided the coin-cell supply remains connected to the chip.

A second write of [0xB1, 0xFE, 0xA3] to the password register resets the FSEAL bit to 0. The three bytes must be written consecutively for the sequence to be valid.

A third write of [0xB1, 0xFE, 0xA3] to the password register sets the FSEAL bit to 1 and locks it into this state for as long as the coin-cell supply (CC) remains connected to the chip.

8.5.3 The FLAG Register

The FLAG register contains a bit for each power rail and GPO to keep track of the enable state of the rails while the system is suspended. The following rules apply to the FLAG register:

- The power-up default value for any flag bit is 0.
- Flag bits are read-only and cannot be written to.
- Upon entering a SUSPEND state, the flag bits are set to same value as their corresponding ENABLE bits.
 Rails and GPOs enabled in a SUSPEND state have flag bits set to 1, while all other flag bits are set to 0. Flag bits are not updated while in the SUSPEND state or when exiting the SUSPEND state.
- The FLAG register is static in WAIT_PWR_EN and ACTIVE state. The FLAG register reflects the enable state of DCDC1, 2, 3, 4, LDO1, and GPO1, 2, 3 during the last SUSPEND state.

The host processor reads the FLAG register to determine if the system powered up from the OFF or SUSPEND state. In the SUSPEND state, typically the DDR memory is kept in self refresh mode and therefore the DC3_FLG or DC4_FLG bits are set.

Registers (continued)

8.5.4 TPS65218 Registers

Table 6 lists the memory-mapped registers for the TPS65218. All register offset addresses not listed in Table 6 should be considered as reserved locations and the register contents should not be modified.

Table 6. TPS65218 Registers

Sub- Address	Acronym	Register Name	R/W	Password Protected	Section
0x0h	CHIPID	CHIP ID	R	No	CHIPID Register (sub- address = 0x0h) [reset = 0x1h]
0x1h	INT1	INTERRUPT 1	R	No	INT1 Register (sub- address= 0x1h) [reset = 0x0h]
0x2h	INT2	INTERRUPT 2	R	No	INT2 Register (sub- address = 0x2h) [reset = 0x0h]
0x3h	INT_MASK1	INTERRUPT MASK 1	R/W	No	INT_MASK1 Register (sub-address = 0x3h) [reset = 0x0h]
0x4h	INT_MASK2	INTERRUPT MASK 2	R/W	No	INT_MASK2 Register (sub-address = 0x4h) [reset = 0x0h]
0x5h	STATUS	STATUS	R	No	STATUS Register (sub-address = 0x5h) [reset = 0x0h]
0x6h	CONTROL	CONTROL	R/W	No	CONTROL Register (sub-address = 0x6h) [reset = 0x0h]
0x7h	FLAG	FLAG	R	No	FLAG Register (sub- address = 0x7h) [reset = 0x0h]
0x10h	PASSWORD	PASSWORD	R/W	No	PASSWORD Register (sub-address = 0x10h) [reset = 0x0h]
0x11h	ENABLE1	ENABLE 1	R/W	Yes	ENABLE1 Register (sub-address = 0x11h) [reset = 0x0h]
0x12h	ENABLE2	ENABLE 2	R/W	Yes	ENABLE2 Register (sub-address = 0x12h) [reset = 0x0h]
0x13h	CONFIG1	CONFIGURATION 1	R/W	Yes	CONFIG1 Register (sub-address = 0x13h) [reset = 0x48h]
0x14h	CONFIG2	CONFIGURATION 2	R/W	Yes	CONFIG2 Register (sub-address = 0x14h) [reset = 0xC0h]
0x15h	CONFIG3	CONFIGURATION 3	R/W	Yes	CONFIG3 Register (sub-address = 0x15h) [reset = 0x0h]
0x16h	DCDC1	DCDC1 CONTROL	R/W	Yes	DCDC1 Register (offset = 0x16h) [reset = 0x99h]
0x17h	DCDC2	DCDC2 CONTROL	R/W	Yes	DCDC2 Register (sub- address = 0x17h) [reset = 0x99h]
0x18h	DCDC3	DCDC3 CONTROL	R/W	Yes	DCDC3 Register (sub- address = 0x18h) [reset = 0x8Ch]

TEXAS INSTRUMENTS

Registers (continued)

Table 6. TPS65218 Registers (continued)

Sub- Address	Acronym	Register Name	R/W	Password Protected	Section
0x19h	DCDC4	DCDC4 CONTROL	R/W	Yes	DCDC4 Register (sub- address = 0x19h) [reset = 0xB2h]
0x1Ah	SLEW	SLEW RATE CONTROL	R/W	Yes	SLEW Register (sub- address = 0x1Ah) [reset = 0x6h]
0x1Bh	LDO1	LDO1 CONTROL	R/W	Yes	LDO1 Register (sub- address = 0x1Bh) [reset = 0x1Fh]
0x20h	SEQ1	SEQUENCER 1	R/W	Yes	SEQ1 Register (sub- address = 0x20h) [reset = 0x0h]
0x21h	SEQ2	SEQUENCER 2	R/W	Yes	SEQ2 Register (sub- address = 0x21h) [reset = 0x0h]
0x22h	SEQ3	SEQUENCER 3	R/W	Yes	SEQ3 Register (sub- address = 0x22h) [reset = 0x98h]
0x23h	SEQ4	SEQUENCER 4	R/W	Yes	SEQ4 Register (sub- address = 0x23h) [reset = 0x75h]
0x24h	SEQ5	SEQUENCER 5	R/W	Yes	SEQ5 Register (sub- address = 0x24h) [reset = 0x12h]
0x25h	SEQ6	SEQUENCER 6	R/W	Yes	SEQ6 Register (sub- address = 0x25h) [reset = 0x63h]
0x26h	SEQ7	SEQUENCER 7	R/W	Yes	SEQ7 Register (sub- address = 0x26h) [reset = 0x3h]



8.5.4.1 CHIPID Register (sub-address = 0x0h) [reset = 0x1h]

CHIPID is shown in Figure 35 and described in Table 7.

Figure 35. CHIPID Register



Table 7. CHIPID Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-3	CHIP	R	0h	Chip ID
				00000b = TPS65218
				00001b = Future use
				11111b = Future use
2-0	REV	R	3h	Revision code
				000b = Revision 1.0
				001b = Revision 1.1
				010b = Revision 2.0
				011b = Revision 2.1
				111b = Future use



8.5.4.2 INT1 Register (sub-address= 0x1h) [reset = 0x0h]

INT1 is shown in Figure 36 and described in Table 8.

Figure 36. INT1 Register

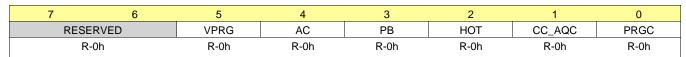


Table 8. INT1 Register Field Descriptions

	Table 6. INTT Register Field Descriptions						
Bit	Field	Туре	Reset	Description			
7-6	RESERVED	R	0h				
5	VPRG	R	0h	Programming voltage interrupt 0b = No significance			
				1b = Input voltage is too low for programming power-up default values.			
4	AC	R	0h	AC_DET pin status change interrupt. Note: Status information is available in STATUS register			
				0b = No change in status			
				1b = AC_DET status change (AC_DET pin changed high to low or low to high)			
3	РВ	R	0h	Push-button status change interrupt. Note: Status information is available in STATUS register			
				0b = No change in status			
				1b = Push-button status change (PB changed high to low or low to high)			
2	HOT	R	0h	Thermal shutdown early warning			
				0b = Chip temperature is below HOT threshold			
				1b = Chip temperature exceeds HOT threshold			
1	CC_AQC	R	0h	Coin cell battery voltage acquisition complete interrupt			
				0b = No significance			
				1b = Backup battery status comparators have settled and results are available in STATUS register			
0	PRGC	R	0h	EEPROM programming complete interrupt			
				0b = No significance			
				1b = Programming of power-up default settings has completed successfully			



8.5.4.3 INT2 Register (sub-address = 0x2h) [reset = 0x0h]

INT2 is shown in Figure 37 and described in Table 9.

Figure 37. INT2 Register

7	6	5	4	3	2	1	0
RESE	RVED	LS3_F	LS2_F	LS1_F	LS3_I	LS2_I	LS1_I
R-	0h	R-0h	R-0h	R-0h	R-0h	R-0h	R-0h

Table 9. INT2 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-6	RESERVED	R	0h	
5	LS3_F	R	0h	Load switch3 fault interrupt 0b = No fault. Switch is working normally.
				1b = Load switch exceeded operating temperature limit and is temporarily disabled.
4	LS2_F	R	0h	Load switch2 fault interrupt
				0b = No fault. Switch is working normally.
				1b = Load switch exceeded operating temperature limit or input voltage dropped below minimum value. Switch is temporarily disabled.
3	LS1_F	R	0h	Load switch1 fault interrupt
				0b = No fault. Switch is working normally.
				1b = Load switch exceeded operating temperature limit and is temporarily disabled.
2	LS3_I	R	0h	Load switch3 current-limit interrupt
				0b = Load switch is disabled or not in current limit
				1b = Load switch is actively limiting the output current (output load is exceeding current limit value)
1	LS2_I	R	0h	Load switch2 current-limit interrupt
				0b = Load switch is disabled or not in current limit
				1b = Load switch is actively limiting the output current (output load is exceeding current limit value)
0	LS1_I	R	0h	Load switch1 current-limit interrupt
				0b = Load switch is disabled or not in current limit
				1b = Load switch is actively limiting the output current (output load is exceeding current limit value)



8.5.4.4 INT_MASK1 Register (sub-address = 0x3h) [reset = 0x0h]

INT_MASK1 is shown in Figure 38 and described in Table 10.

Figure 38. INT_MASK1 Register

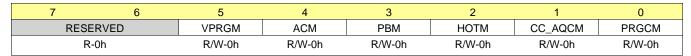


Table 10. INT_MASK1 Register Field Descriptions

			_	
Bit	Field	Туре	Reset	Description
7-6	RESERVED	R	0h	
5	VPRGM	R/W	0h	Programming voltage interrupt mask bit. Note: mask bit has no effect on monitoring function
				0b = Interrupt is un-masked (interrupt event pulls nINT pin low)
				1b = Interrupt is masked (interrupt has no effect on nINT pin)
4	ACM	R/W	0h	AC_DET interrupt masking bit.
				0b = Interrupt is un-masked (interrupt event pulls nINT pin low)
				1b = Interrupt is masked (interrupt has no effect on nINT pin)
				Note: mask bit has no effect on monitoring function
3	PBM	R/W	0h	PB interrupt masking bit. Note: mask bit has no effect on monitoring function
				0b = Interrupt is un-masked (interrupt event pulls nINT pin low)
				1b = Interrupt is masked (interrupt has no effect on nINT pin)
2	НОТМ	R/W	0h	HOT interrupt masking bit. Note: mask bit has no effect on monitoring function
				0b = Interrupt is un-masked (interrupt event pulls nINT pin low)
				1b = Interrupt is masked (interrupt has no effect on nINT pin)
1	CC_AQCM	R/W	0h	C_AQC interrupt masking bit. Note: mask bit has no effect on monitoring function
				0b = Interrupt is un-masked (interrupt event pulls nINT pin low)
				1b = Interrupt is masked (interrupt has no effect on nINT pin)
0	PRGCM	R/W	0h	PRGC interrupt masking bit. Note: mask bit has no effect on monitoring function
				0b = Interrupt is un-masked (interrupt event pulls nINT pin low)
				1b = Interrupt is masked (interrupt has no effect on nINT pin)

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8.5.4.5 INT_MASK2 Register (sub-address = 0x4h) [reset = 0x0h]

INT_MASK2 is shown in Figure 39 and described in Table 11.

Figure 39. INT_MASK2 Register

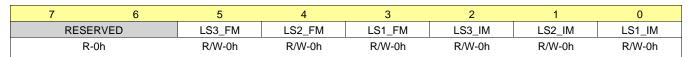


Table 11. INT_MASK2 Register Field Descriptions

Bit				
Dit	Field	Туре	Reset	Description
7-6	RESERVED	R	0h	
5	LS3_FM	R/W	0h	LS3 fault interrupt mask bit. Note: mask bit has no effect on monitoring function
				0b = Interrupt is un-masked (interrupt event pulls nINT pin low)
				1b = Interrupt is masked (interrupt has no effect on nINT pin)
4	LS2_FM	R/W	0h	LS2 fault interrupt mask bit. Note: mask bit has no effect on monitoring function
				0b = Interrupt is un-masked (interrupt event pulls nINT pin low)
				1b = Interrupt is masked (interrupt has no effect on nINT pin)
3	LS1_FM	R/W	0h	LS1 fault interrupt mask bit. Note: mask bit has no effect on monitoring function
				0b = Interrupt is un-masked (interrupt event pulls nINT pin low)
				1b = Interrupt is masked (interrupt has no effect on nINT pin)
2	LS3_IM	R/W	0h	LS3 current-limit interrupt mask bit. Note: mask bit has no effect on monitoring function
				0b = Interrupt is un-masked (interrupt event pulls nINT pin low)
				1b = Interrupt is masked (interrupt has no effect on nINT pin)
1	LS2_IM	R/W	0h	LS2 current-limit interrupt mask bit. Note: mask bit has no effect on monitoring function
				0b = Interrupt is un-masked (interrupt event pulls nINT pin low)
				1b = Interrupt is masked (interrupt has no effect on nINT pin)
0	LS1_IM	R/W	0h	LS1 current-limit interrupt mask bit. Note: mask bit has no effect on monitoring function
				0b = Interrupt is un-masked (interrupt event pulls nINT pin low)
				1b = Interrupt is masked (interrupt has no effect on nINT pin)

Instruments

8.5.4.6 STATUS Register (sub-address = 0x5h) [reset = 0x0h]

Register mask: C0h

STATUS is shown in Figure 40 and described in Table 12.

Figure 40. STATUS Register

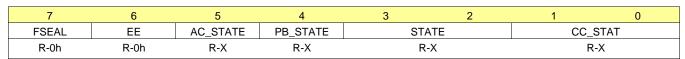


Table 12. STATUS Register Field Descriptions

Bit	Field	Туре	Reset	Description
7	FSEAL	R	Oh	Freshness seal (FSEAL) status. Note: See for details. 0b = FSEAL is in native state (fresh) 1b = FSEAL is broken
6	EE	R	Oh	EEPROM status 0b = EEPROM values have not been changed from factory default setting 1b = EEPROM values have been changed from factory default settings
5	AC_STATE	R	X	AC_DET input status bit 0b = AC_DET input is inactive (AC_DET input pin is low) 1b = AC_DET input is active (AC_DET input is high)
4	PB_STATE	R	X	PB input status bit 0b = Push Button input is inactive (PB input pin is high) 1b = Push Button input is active (PB input pin is low)
3-2	STATE	R	X	State machine STATE indication 00b = PMIC is in transitional state 01b = PMIC is in WAIT_PWR_EN state 10b = PMIC is in ACTIVE state 11b = PMIC is in SUSPEND state
1-0	CC_STAT	R	X	Coin cell state of charge. Note: Coin-cell voltage acquisition must be triggered first before status bits are valid. See CC_AQ bit in CONTROL Register (sub-address = 0x6h) [reset = 0x0h]. $00b = V_{CC} < V_{LOW_LEVEL}; \text{ Coin cell is not present or approaching end-of-life (EOL)} \\ 01b = V_{LOW_LEVEL} < V_{CC} < V_{GOOD_LEVEL}; \text{ Coin cell voltage is LOW.} \\ 10b = V_{GOOD_LEVEL} < V_{CC} < V_{IDEAL_LEVEL}; \text{ Coin cell voltage is GOOD.} \\ 11b = V_{IDEAL} < V_{CC}; \text{ Coin cell voltage is IDEAL.} $



8.5.4.7 CONTROL Register (sub-address = 0x6h) [reset = 0x0h]

CONTROL is shown in Figure 41 and described in Table 13.

Figure 41. CONTROL Register



Table 13. CONTROL Register Field Descriptions

				-
Bit	Field	Туре	Reset	Description
7-2	RESERVED	R	0h	
1	OFFnPFO	R/W	0h	Power-fail shutdown bit 0b = nPFO has no effect on PMIC state
				1b = All rails are shut down and PMIC enters OFF state when PFI comparator trips (nPFO is low)
0	CC_AQ	R/W	0h	Coin Cell battery voltage acquisition start bit 0b = No significance
				1b = Triggers voltage acquisition. Bit is automatically reset to 0.

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8.5.4.8 FLAG Register (sub-address = 0x7h) [reset = 0x0h]

FLAG is shown in Figure 42 and described in Table 14.

Figure 42. FLAG Register

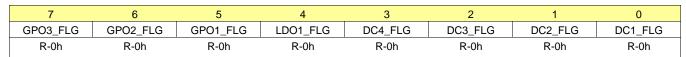


Table 14. FLAG Register Field Descriptions

Bit	Field	Туре	Reset	Description
7	GPO3_FLG	R	Oh	•
,	01 03_1 20	IX.	OII	GPO3 Flag bit
				0b = Device powered up from OFF or SUSPEND state and GPO3 was disabled while in SUSPEND.
				1b = Device powered up from SUSPEND state and GPO3 was enabled while in SUSPEND.
6	GPO2_FLG	R	0h	GPO2 Flag bit
				0b = Device powered up from OFF or SUSPEND state and GPO2 was disabled while in SUSPEND.
				1b = Device powered up from SUSPEND state and GPO2 was enabled while in SUSPEND.
5	GPO1_FLG	R	0h	GPO1 Flag bit
				0b = Device powered up from OFF or SUSPEND state and GPO1 was disabled while in SUSPEND.
				1b = Device powered up from SUSPEND state and GPO1 was enabled while in SUSPEND.
4	LDO1_FLG	R	0h	LDO1 Flag bit
				0b = Device powered up from OFF or SUSPEND state and LDO1 was disabled while in SUSPEND.
				1b = Device powered up from SUSPEND state and LDO1 was enabled while in SUSPEND.
3	DC4_FLG	R	0h	DCDC4 Flag bit
				0b = Device powered up from OFF or SUSPEND state and DCDC4 was disabled while in SUSPEND.
				1b = Device powered up from SUSPEND state and DCDC4 was enabled while in SUSPEND.
2	DC3_FLG	R	0h	DCDC3 Flag bit
				0b = Device powered up from OFF or SUSPEND state and DCDC3 was disabled while in SUSPEND.
				1b = Device powered up from SUSPEND state and DCDC3 was enabled while in SUSPEND.
1	DC2_FLG	R	0h	DCDC2 Flag bit
				0b = Device powered up from OFF or SUSPEND state and DCDC2 was disabled while in SUSPEND.
				1b = Device powered up from SUSPEND state and DCDC2 was enabled while in SUSPEND.
0	DC1_FLG	R	0h	DCDC1 Flag bit
				0b = Device powered up from OFF or SUSPEND state and DCDC1 was disabled while in SUSPEND.
				1b = Device powered up from SUSPEND state and GDCDC1PO3 was enabled while in SUSPEND.



8.5.4.9 PASSWORD Register (sub-address = 0x10h) [reset = 0x0h]

PASSWORD is shown in Figure 43 and described in Table 15.

Figure 43. PASSWORD Register

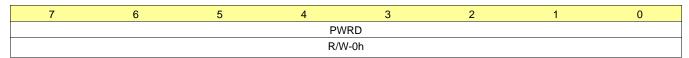


Table 15. PASSWORD Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-0	PWRD	R/W	0h	Register is used for: Accessing password protected registers (see Password Protection for details). Breaking the freshness seal (see The Freshness Seal (FSEAL) Bit for details). Programming power-up default values (see Programming power-up default values for details). Read-back always yields 0x00.

8.5.4.10 ENABLE1 Register (sub-address = 0x11h) [reset = 0x0h]

ENABLE1 is shown in Figure 44 and described in Table 16.

Password protected.

Figure 44. ENABLE1 Register

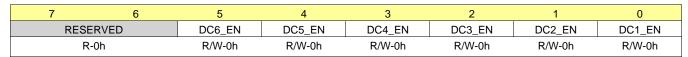


Table 16. ENABLE1 Register Field Descriptions

Table 10. ENABLET Register Fleid Descriptions							
Bit	Field	Туре	Reset	Description			
7-6	RESERVED	R	0h				
5	DC6_EN	R/W	0h	DCDC6 enable bit. DCDC6 can only be disabled if FSEAL = 0. See The Freshness Seal (FSEAL) Bit for details. 0b = Disabled 1b = Enabled			
4	DC5_EN	R/W	Oh	DCDC5 enable bit. Note: At power-up/down this bit is automatically updated by the internal power sequencer. DCDC5 can only be disabled if FSEAL = 0. See The Freshness Seal (FSEAL) Bit for details. 0b = Disabled 1b = Enabled			
3	DC4_EN	R/W	0h	DCDC4 enable bit. Note: At power-up/down this bit is automatically updated by the internal power sequencer. 0b = Disabled 1b = Enabled			
2	DC3_EN	R/W	0h	DCDC3 enable bit. Note: At power-up/down this bit is automatically updated by the internal power sequencer. 0b = Disabled 1b = Enabled			
1	DC2_EN	R/W	0h	DCDC2 enable bit. Note: At power-up/down this bit is automatically updated by the internal power sequencer. 0b = Disabled 1b = Enabled			
0	DC1_EN	R/W	0h	DCDC1 enable bit. Note: At power-up/down this bit is automatically updated by the internal power sequencer. 0b = Disabled 1b = Enabled			

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ISTRUMENTS



8.5.4.11 ENABLE2 Register (sub-address = 0x12h) [reset = 0x0h]

ENABLE2 is shown in Figure 45 and described in Table 17.

Password protected.

Figure 45. ENABLE2 Register

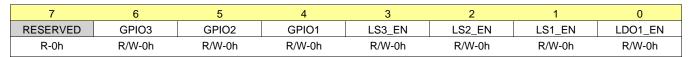


Table 17. ENABLE2 Register Field Descriptions

				register i leid Descriptions
Bit	Field	Туре	Reset	Description
7	RESERVED	R	0h	
6	GPIO3	R/W	0h	General purpose output 3 / reset polarity. Note: If DC12_RST bit (register 0x14) is set to 1 this bit has no function.
				0b = GPIO3 output is driven low
				1b = GPIO3 output is HiZ
5	GPIO2	R/W	0h	General purpose output 2. Note: If IO_SEL bit (register 0x13) is set to 1 this bit has no function.
				0b = GPO2 output is driven low
				1b = GPO2 output is HiZ
4	GPIO1	R/W	0h	General purpose output 1. Note: If IO_SEL bit (register 0x13) is set to 1 this bit has no function.
				0b = GPO1 output is driven low
				1b = GPO1 output is HiZ
3	LS3_EN	R/W	0h	Load switch 3 (LS3) enable bit
				0b = Disabled
				1b = Enabled
2	LS2_EN	R/W	0h	Load switch 2 (LS2) enable bit
				0b = Disabled
				1b = Enabled
1	LS1_EN	R/W	0h	Load switch 1 (LS1) enable bit.
				0b = Disabled
				1b = Enabled
				Note: At power-up/down this bit is automatically updated by the
				internal power sequencer.
0	LDO1_EN	R/W	0h	LDO1 enable bit.
				0b = Disabled
				1b = Enabled
				Note: At power-up/down this bit is automatically updated by the internal power sequencer.

Instruments

8.5.4.12 CONFIG1 Register (sub-address = 0x13h) [reset = 0x48h]

CONFIG1 is shown in Figure 46 and described in Table 18.

Password protected.

Figure 46. CONFIG1 Register

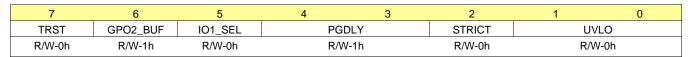


Table 18. CONFIG1 Register Field Descriptions

		14510 101		register i leiu Descriptions
Bit	Field	Туре	Reset	Description
7	TRST	R/W	0h	Push-button reset time constant 0b = 8s 1b = 15s
6	GPO2_BUF	R/W	1h	GPO2 output buffer configuration 0b = GPO2 buffer is configured as open-drain 1b = GPO2 buffer is configured as push-pull (high-level is driven to IN_LS1)
5	IO1_SEL	R/W	0h	GPIO1 / GPO2 configuration bit. See I/O Configuration for details. 0b = GPIO1 is configured as general-purpose, open-drain output. GPO2 is independent output 1b = GPIO1 is configured as input, controlling GPO2. Intended for
4-3	PGDLY	R/W	1h	DDR3 reset signal control. Power-Good delay. Note: Power-good delay applies to rising-edge only (power-up), not falling edge (power-down or fault) 00b = 10ms 01b = 20ms 10b = 50ms 11b = 150ms
2	STRICT	R/W	Oh	Supply Voltage Supervisor Sensitivity selection. See Electrical Characteristics for details. Ob = Power-good threshold (VOUT falling) has wider limits. Overvoltage is not monitored 1b = Power-good threshold (VOUT falling) has tight limits. Overvoltage is monitored.
1-0	UVLO	R/W	Oh	Under Voltage Lock Out setting 00b = 2.75 V 01b = 2.95 V 10b = 3.25 V 11b = 3.35 V



8.5.4.13 CONFIG2 Register (sub-address = 0x14h) [reset = 0xC0h]

CONFIG2 is shown in Figure 47 and described in Table 19.

Password protected.

Figure 47. CONFIG2 Register

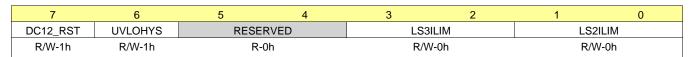


Table 19. CONFIG2 Register Field Descriptions

D:4	Field	Tyma	Dooot	Description
Bit		Туре	Reset	Description
7	DC12_RST	R/W	1h	DCDC1 and DCDC2 reset-pin enable
				0b = GPIO3 is configured as general-purpose output
				1b = GPIO3 is configured as warm-reset input to DCDC1 and DCDC2
6	UVLOHYS	R/W	1h	UVLO hysteresis
				0b = 200 mV
				1b = 400 mV
5-4	RESERVED	R	0h	
3-2	LS3ILIM	R/W	0h	Load switch 3 (LS3) current limit selection
				00b = 100 mA
				01b = 200 mA
				10b = 500 mA
				11b = 1000 mA
1-0	LS2ILIM	R/W	0h	Load switch 2 (LS2) current limit selection
				00b = 100 mA
				01b = 200 mA
				10b = 500 mA
				11b = 1000 mA



8.5.4.14 CONFIG3 Register (sub-address = 0x15h) [reset = 0x0h]

CONFIG3 is shown in Figure 48 and described in Table 20.

Password protected.

Figure 48. CONFIG3 Register

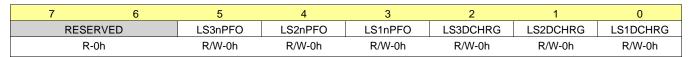


Table 20. CONFIG3 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-6	RESERVED	R	0h	
5	LS3nPFO	R/W	0h	Load switch 3 power-fail disable bit
				0b = Load switch status is not affected by power-fail comparator
				1b = Load switch is disabled if power-fail comparator trips (nPFO is low)
4	LS2nPFO	R/W	0h	Load switch 2 power-fail disable bit
				0b = Load switch status is not affected by power-fail comparator
				1b = Load switch is disabled if power-fail comparator trips (nPFO is low)
3	LS1nPFO	R/W	0h	Load switch 1 power-fail disable bit
				0b = Load switch status is not affected by power-fail comparator
				1b = Load switch is disabled if power-fail comparator trips (nPFO is low)
2	LS3DCHRG	R/W	0h	Load switch 3 discharge enable bit
				0b = Active discharge is disabled
				1b = Active discharge is enabled (load switch output is actively discharged when switch is OFF)
1	LS2DCHRG	R/W	0h	Load switch 2 discharge enable bit
				0b = Active discharge is disabled
				1b = Active discharge is enabled (load switch output is actively discharged when switch is OFF)
0	LS1DCHRG	R/W	0h	Load switch 1 discharge enable bit
				0b = Active discharge is disabled
				1b = Active discharge is enabled (load switch output is actively discharged when switch is OFF)



8.5.4.15 DCDC1 Register (offset = 0x16h) [reset = 0x99h]

DCDC1 is shown in Figure 49 and described in Table 21.

Password protected.

Figure 49. DCDC1 Register



Table 21. DCDC1 Register Field Descriptions

	Table 21. Dobot Register Field Descriptions								
Bit	Field	Туре	Reset	Description					
7	PFM	R/W	1h	Pulse Frequency Modulation (PFM, also known as pulse-skip-mode) enable. PFM mode improves light-load efficiency. Actual PFM mode operation depends on load condition. Ob = Disabled (forced PWM)					
				1b = Enabled					
6	RESERVED	R	0h						
5-0	DCDC1	R/W	19h	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$					

Instruments

8.5.4.16 DCDC2 Register (sub-address = 0x17h) [reset = 0x99h]

DCDC2 is shown in Figure 50 and described in Table 22.

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Figure 50. DCDC2 Register



Table 22. DCDC2 Register Field Descriptions

Bit	Field	Туре	Reset	Description			
7	PFM	R/W	1h	Pulse Frequency Modu mode improves light-loa condition. Ob = Disabled (forced P\ 1b = Enabled	ad efficiency. Actual		
6	RESERVED	R	0h				
5-0	DCDC2	R/W	19h	DCDC2 output voltage setting 000000b = 0.850 000001b = 0.860 000010b = 0.870 000011b = 0.880 000100b = 0.890 000101b = 0.900 000110b = 0.910 000111b = 0.920 001000b = 0.930 001001b = 0.940 001010b = 0.950 001101b = 0.960 001100b = 0.970 001101b = 0.980 001111b = 0.990 001111b = 1.000	010000b = 1.010 010001b = 1.020 010010b = 1.030 010011b = 1.040 010100b = 1.050 010101b = 1.060 010110b = 1.070 010111b = 1.080 011000b = 1.090 011001b = 1.100 011010b = 1.110 011011b = 1.120 011100b = 1.130 011101b = 1.140 011111b = 1.150 011111b = 1.160	100000b = 1.170 100001b = 1.180 100010b = 1.190 100011b = 1.200 100100b = 1.210 100101b = 1.220 100110b = 1.230 100111b = 1.240 101000b = 1.250 101010b = 1.270 101011b = 1.280 101101b = 1.280 101100b = 1.290 101101b = 1.300 101111b = 1.310 101111b = 1.320	110000b = 1.330 110001b = 1.340 110010b = 1.350 110011b = 1.375 110100b = 1.400 110101b = 1.425 110110b = 1.450 110111b = 1.475 111000b = 1.500 111010b = 1.550 111011b = 1.575 111100b = 1.600 111101b = 1.625 111110b = 1.650 111111b = 1.675

8.5.4.17 DCDC3 Register (sub-address = 0x18h) [reset = 0x8Ch]

DCDC3 is shown in Figure 51 and described in Table 23.

Note: Power-up default may differ depending on RSEL value. See DCDC3 POWER-UP DEFAULT SELECTION for details.

Figure 51. DCDC3 Register

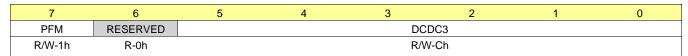


Table 23. DCDC3 Register Field Descriptions

				20200 Rogiotor Flora 2000 Iptiono
Bit	Field	Туре	Reset	Description
7	PFM	R/W	1h	Pulse Frequency Modulation (PFM, also known as pulse-skip-mode) enable. PFM mode improves light-load efficiency. Actual PFM mode operation depends on load condition.
				0h = Disabled (forced PWM)
				1h = Enabled
6	RESERVED	R	0h	
5-0	DCDC3	R/W	Ch	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$



8.5.4.18 DCDC4 Register (sub-address = 0x19h) [reset = 0xB2h]

DCDC4 is shown in Figure 52 and described in Table 24.

Note: Power-up default may differ depending on RSEL value. See DCDC4 POWER-UP DEFAULT SELECTION for details. The Reserved setting should not be selected and the output voltage settings should not be modified while the converter is operating.

Figure 52. DCDC4 Register

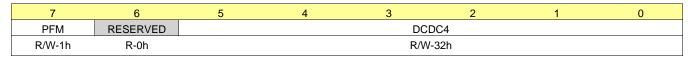


Table 24. DCDC4 Register Field Descriptions

Bit	Field	Туре	Reset	Description		•		
7	PFM	R/W	1h	Pulse Frequency Modulation (PFM, also known as pulse-skip-mode) enable. PFM				
				improves light-load ef	ficiency. Actual PFM	mode operation deper		
				0b = Disabled (forced	PWM)			
				1b = Enabled				
6	RESERVED	R	0h					
5-0	DCDC4	R/W	32h	DCDC4 output	010000b = 1.600	100000b = 2.400	110000b = 3.200	
				voltage setting	010001b = 1.650	100001b = 2.450	110001b = 3.250	
				000000b = 1.175	010010b = 1.700	100010b = 2.500	110010b = 3.300	
				000001b = 1.200	010011b = 1.750	100011b = 2.550	110011b = 3.350	
				000010b = 1.225	010100b = 1.800	100100b = 2.600	110100b = 3.400	
				000011b = 1.250	010101b = 1.850	100101b = 2.650	110101b = reserved	
				000100b = 1.275	010110b = 1.900	100110b = 2.700	110110b = reserved	
				000101b = 1.300	010111b = 1.950	100111b = 2.750	110111b = reserved	
				000110b = 1.325	011000b = 2.000	101000b = 2.800	111000b = reserved	
				000111b = 1.350	011001b = 2.050	101001b = 2.850	111001b = reserved	
				001000b = 1.375	011010b = 2.100	101010b = 2.900	111010b = reserved	
				001001b = 1.400	011011b = 2.150	101011b = 2.950	111011b = reserved	
				001010b = 1.425	011100b = 2.200	101100b = 3.000	111100b = reserved	
				001011b = 1.450	011101b = 2.250	101101b = 3.050	111101b = reserved	
				001100b = 1.475	011110b = 2.300	101110b = 3.100	111110b = reserved	
				001101b = 1.500	011111b = 2.3500	101111b = 3.150	111111b = reserved	
				001110b = 1.525				
				001111b = 1.550				

8.5.4.19 SLEW Register (sub-address = 0x1Ah) [reset = 0x6h]

SLEW is shown in Figure 53 and described in Table 25.

Note: Slew-rate control applies to DCDC1 and DCDC2 only. If changing from a higher voltage to lower voltage while STRICT=1 and converters are in a no load state, PFM bit for DCDC1 and DCDC2 must be set to 0.

Figure 53. SLEW Register

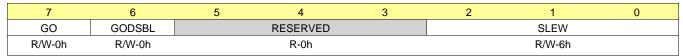


Table 25. SLEW Register Field Descriptions

		10010 20	. 0	gister i leid bescriptions
Bit	Field	Туре	Reset	Description
7	GO	R/W	0h	Go bit. Note: Bit is automatically reset at the end of the voltage transition
				0b = No change
				1b = Initiates the transition from present state to the output voltage setting currently stored in DCDC1 / DCDC2 register. SLEW setting does apply.
6	GODSBL	R/W	0h	Go disable bit
				0b = Enabled
				1b = Disabled; DCDC1 and DCDC2 output voltage changes whenever set-point is updated in DCDC1 / DCDC2 register without having to write to the GO bit. SLEW setting does apply.
5-3	RESERVED	R	0h	
2-0	SLEW	R/W	6h	Output slew rate setting
				000b = 160 us/step (0.0625 mV/ s at 10 mV per step)
				001b = 80 us/step (0.125 mV/ s at 10 mV per step)
				010b = 40 us/step (0.250 mV/ s at 10 mV per step)
				011b = 20 us/step (0.500 mV/ s at 10 mV per step)
				100b = 10 us/step (1.0 mV/ s at 10 mV per step)
				101b = 5 us/step (2.00 mV/ s at 10 mV per step)
				110b = 2.5 us/step (4.0 mV/ s at 10 mV per step)
				111b = Immediate; Slew rate is only limited by control loop response time. Note: The actual slew rate depends on the voltage step per code. Refer to DCDCx registers for details.

TEXAS INSTRUMENTS

8.5.4.20 LDO1 Register (sub-address = 0x1Bh) [reset = 0x1Fh]

LDO1 is shown in Figure 54 and described in Table 26.

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Figure 54. LDO1 Register



Table 26. LDO1 Register Field Descriptions

Bit	Field	Type	Reset	Description			
7-6	RESERVED	R	0h				
5-0	LDO1	R/W	1Fh	LDO1 output voltage setting 000000b = 0.900 000001b = 0.925 000010b = 0.950 000011b = 0.975 000100b = 1.025 000110b = 1.025 00110b = 1.125 001010b = 1.125 001010b = 1.175 001100b = 1.175 001100b = 1.200 00111b = 1.225 001110b = 1.250 001111b = 1.275	010000b = 1.300 010001b = 1.325 010010b = 1.350 010011b = 1.375 010100b = 1.400 010101b = 1.425 010110b = 1.450 010111b = 1.475 011000b = 1.500 011001b = 1.525 011010b = 1.550 011011b = 1.600 011100b = 1.650 011101b = 1.700 011110b = 1.750 011111b = 1.750 011111b = 1.800	100000b = 1.850 100001b = 1.900 100010b = 1.950 100011b = 2.000 100100b = 2.050 100101b = 2.100 100110b = 2.150 100111b = 2.200 101000b = 2.250 101001b = 2.350 101011b = 2.400 101100b = 2.450 101100b = 2.500 101101b = 2.500 101110b = 2.550 101111b = 2.600	110000b = 2.650 110001b = 2.700 110010b = 2.750 110011b = 2.800 110100b = 2.850 110101b = 2.900 110110b = 2.950 110111b = 3.000 111000b = 3.050 111001b = 3.150 111011b = 3.200 111101b = 3.250 111101b = 3.350 111110b = 3.350 111110b = 3.350 111111b = 3.400

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8.5.4.21 SEQ1 Register (sub-address = 0x20h) [reset = 0x0h]

SEQ1 is shown in Figure 55 and described in Table 27.

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Figure 55. SEQ1 Register

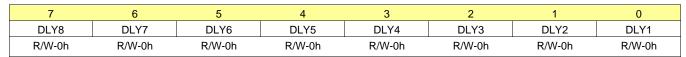


Table 27. SEQ1 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7	DLY8	R/W	0h	Delay8 (occurs after Stobe8 and before Strobe9) 0b = 2 ms 1b = 5 ms
6	DLY7	R/W	0h	Delay7 (occurs after Stobe7 and before Strobe8) 0b = 2 ms 1b = 5 ms
5	DLY6	R/W	0h	Delay6 (occurs after Stobe6 and before Strobe7) 0b = 2 ms 1b = 5 ms
4	DLY5	R/W	0h	Delay5 (occurs after Stobe5 and before Strobe6) 0b = 2 ms 1b = 5 ms
3	DLY4	R/W	0h	Delay4 (occurs after Stobe4 and before Strobe5) 0b = 2 ms 1b = 5 ms
2	DLY3	R/W	0h	Delay3 (occurs after Stobe3 and before Strobe4) 0b = 2 ms 1b = 5 ms
1	DLY2	R/W	0h	Delay2 (occurs after Stobe2 and before Strobe3) 0b = 2 ms 1b = 5 ms
0	DLY1	R/W	0h	Delay1 (occurs after Stobe1 and before Strobe2) 0b = 2 ms 1b = 5 ms

TEXAS INSTRUMENTS

8.5.4.22 SEQ2 Register (sub-address = 0x21h) [reset = 0x0h]

SEQ2 is shown in Figure 56 and described in Table 28.

Password protected.

Figure 56. SEQ2 Register

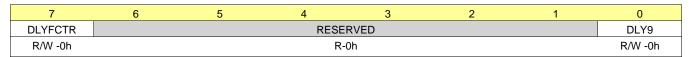


Table 28. SEQ2 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7	DLYFCTR	R/W	0h	Power-down delay factor
				0b = 1x
				1b = 10x (delay times are multiplied by 10x during power-down)
				Note: DLYFCTR has no effect on power-up timing.
6-1	RESERVED	R	0h	
0	DLY9	R/W	0h	Delay9 (occurs after Stobe9 and before Strobe10)
				0b = 2 ms
				1b = 5 ms



8.5.4.23 SEQ3 Register (sub-address = 0x22h) [reset = 0x98h]

SEQ3 is shown in Figure 57 and described in Table 29.

Password protected.

Figure 57. SEQ3 Register

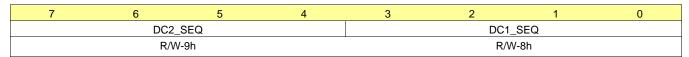


Table 29. SEQ3 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-4	DC2_SEQ	R/W	9h	DCDC2 enable STROBE
		1,7,1,		0000b = Rail is not controlled by sequencer
				0001b = Rail is not controlled by sequencer
				0010b = Rail is not controlled by sequencer 0011b = Enable at STROBE3
				0110b = Enable at STROBE3
				0101b = Enable at STROBE5
				0110b = Enable at STROBES 0110b = Enable at STROBE6
				0111b = Enable at STROBE0
				1000b = Enable at STROBE8
				1000b = Enable at STROBE9
				1010b = Enable at STROBE9
				1011b = Rail is not controlled by sequencer
				1100b = Rail is not controlled by sequencer
				1101b = Rail is not controlled by sequencer
				1110b = Rail is not controlled by sequencer
				1111b = Rail is not controlled by sequencer
3-0	DC1_SEQ	R/W	8h	
3-0	DC1_3EQ	IN/VV	OII	DCDC1 enable STROBE
				0000b = Rail is not controlled by sequencer
				0001b = Rail is not controlled by sequencer
				0010b = Rail is not controlled by sequencer
				0011b = Enable at STROBE3
				0100b = Enable at STROBE4
				0101b = Enable at STROBE5
				0110b = Enable at STROBE6
				0111b = Enable at STROBE7
				1000b = Enable at STROBE8
				1001b = Enable at STROBE9
				1010b = Enable at STROBE10
				1011b = Rail is not controlled by sequencer
				1100b = Rail is not controlled by sequencer
				1101b = Rail is not controlled by sequencer
				1110b = Rail is not controlled by sequencer
				1111b = Rail is not controlled by sequencer

TEXAS INSTRUMENTS

8.5.4.24 SEQ4 Register (sub-address = 0x23h) [reset = 0x75h]

SEQ4 is shown in Figure 58 and described in Table 30.

Password protected.

Figure 58. SEQ4 Register

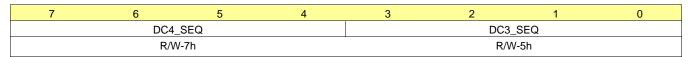


Table 30. SEQ4 Register Field Descriptions

	Table 30. SEQ4 Register Field Descriptions					
Bit	Field	Туре	Reset	Description		
7-4	DC4_SEQ	R/W	7h	DCDC4 enable STROBE		
				0000b = Rail is not controlled by sequencer		
				0001b = Rail is not controlled by sequencer		
				0010b = Rail is not controlled by sequencer		
				0011b = Enable at STROBE3		
				0100b = Enable at STROBE4		
				0101b = Enable at STROBE5		
				0110b = Enable at STROBE6		
				0111b = Enable at STROBE7		
				1000b = Enable at STROBE8		
				1001b = Enable at STROBE9		
				1010b = Enable at STROBE10		
				1011b = Rail is not controlled by sequencer		
				1100b = Rail is not controlled by sequencer		
				1101b = Rail is not controlled by sequencer		
				1110b = Rail is not controlled by sequencer		
				1111b = Rail is not controlled by sequencer		
3-0	DC3_SEQ	R/W	5h	DCDC3 enable STROBE		
				0000b = Rail is not controlled by sequencer		
				0001b = Rail is not controlled by sequencer		
				0010b = Rail is not controlled by sequencer		
				0011b = Enable at STROBE3		
				0100b = Enable at STROBE4		
				0101b = Enable at STROBE5		
				0110b = Enable at STROBE6		
				0111b = Enable at STROBE7		
				1000b = Enable at STROBE8		
				1001b = Enable at STROBE9		
				1010b = Enable at STROBE10		
				1011b = Rail is not controlled by sequencer		
				1100b = Rail is not controlled by sequencer		
				1101b = Rail is not controlled by sequencer		
				1110b = Rail is not controlled by sequencer		
				1111b = Rail is not controlled by sequencer		

8.5.4.25 SEQ5 Register (sub-address = 0x24h) [reset = 0x12h]

SEQ5 is shown in Figure 59 and described in Table 31.

Password protected.

Figure 59. SEQ5 Register

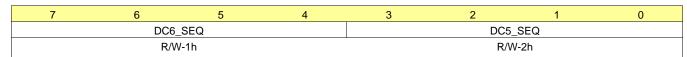


Table 31. SEQ5 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-4	DC6_SEQ	R/W	1h	DCDC6 enable STROBE. Note: Strobe 1 and 2 are executed only if FSEAL = 0. DCDC5 and 6 cannot be disabled by sequencer once freshness seal is broken.
				00b = Rail is not controlled by sequencer
				01b = Enable at STROBE1
				10b = Enable at STROBE2
				11b = Rail is not controlled by sequencer
3-0	DC5_SEQ	R/W	2h	DCDC5 enable STROBE. Note: Strobe 1 and 2 are executed only if FSEAL = 0. DCDC5 and 6 cannot be disabled by sequencer once freshness seal is broken.
				00b = Rail is not controlled by sequencer
				01b = Enable at STROBE1
				10b = Enable at STROBE2
				11b = Rail is not controlled by sequencer

ISTRUMENTS

8.5.4.26 SEQ6 Register (sub-address = 0x25h) [reset = 0x63h]

SEQ6 is shown in Figure 60 and described in Table 32.

Password protected.

Figure 60. SEQ6 Register

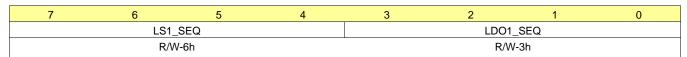


Table 32. SEQ6 Register Field Descriptions

	Table 32. SEQ6 Register Field Descriptions					
Bit	Field	Туре	Reset	Description		
7-4	LS1_SEQ	R/W	6h	LS1 enable STROBE		
				0000b = Rail is not controlled by sequencer		
				0001b = Rail is not controlled by sequencer		
				0010b = Rail is not controlled by sequencer		
				0011b = Enable at STROBE3		
				0100b = Enable at STROBE4		
				0101b = Enable at STROBE5		
				0110b = Enable at STROBE6		
				0111b = Enable at STROBE7		
				1000b = Enable at STROBE8		
				1001b = Enable at STROBE9		
				1010b = Enable at STROBE10		
				1011b = Rail is not controlled by sequencer		
				1100b = Rail is not controlled by sequencer		
				1101b = Rail is not controlled by sequencer		
				1110b = Rail is not controlled by sequencer		
				1111b = Rail is not controlled by sequencer		
3-0	LDO1_SEQ	R/W	3h	LDO1 enable STROBE		
				0000b = Rail is not controlled by sequencer		
				0001b = Rail is not controlled by sequencer		
				0010b = Rail is not controlled by sequencer		
				0011b = Enable at STROBE3		
				0100b = Enable at STROBE4		
				0101b = Enable at STROBE5		
				0110b = Enable at STROBE6		
				0111b = Enable at STROBE7		
				1000b = Enable at STROBE8		
				1001b = Enable at STROBE9		
				1010b = Enable at STROBE10		
				1011b = Rail is not controlled by sequencer		
				1100b = Rail is not controlled by sequencer		
				1101b = Rail is not controlled by sequencer		
				1110b = Rail is not controlled by sequencer		
				1111b = Rail is not controlled by sequencer		

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8.5.4.27 SEQ7 Register (sub-address = 0x26h) [reset = 0x3h]

SEQ7 is shown in Figure 61 and described in Table 33.

Password protected.

Figure 61. SEQ7 Register

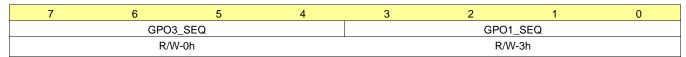


Table 33. SEQ7 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-4	GPO3_SEQ	R/W	0h	•
, ,	01 00_0E&	1000	011	GPO3 enable STROBE
				0000b = Rail is not controlled by sequencer
				0001b = Rail is not controlled by sequencer
				0010b = Rail is not controlled by sequencer
				0011b = Enable at STROBE3
				0100b = Enable at STROBE4
				0101b = Enable at STROBE5
				0110b = Enable at STROBE6
				0111b = Enable at STROBE7
				1000b = Enable at STROBE8
				1001b = Enable at STROBE9
				1010b = Enable at STROBE10
				1011b = Rail is not controlled by sequencer
				1100b = Rail is not controlled by sequencer
				1101b = Rail is not controlled by sequencer
				1110b = Rail is not controlled by sequencer
				1111b = Rail is not controlled by sequencer
3-0	GPO1_SEQ	R/W	3h	GPO1 enable STROBE
				0000b = Rail is not controlled by sequencer
				0001b = Rail is not controlled by sequencer
				0010b = Rail is not controlled by sequencer
				0011b = Enable at STROBE3
				0100b = Enable at STROBE4
				0101b = Enable at STROBE5
				0110b = Enable at STROBE6
				0111b = Enable at STROBE7
				1000b = Enable at STROBE8
				1001b = Enable at STROBE9
				1010b = Enable at STROBE10
				1011b = Rail is not controlled by sequencer
				1100b = Rail is not controlled by sequencer
				1101b = Rail is not controlled by sequencer
				1110b = Rail is not controlled by sequencer
				1111b = Rail is not controlled by sequencer

TEXAS INSTRUMENTS

9 Application and Implementation

9.1 Application Information

The TPS65218 is designed to pair with various application processors. For detailed information on using TPS65218 with Sitara AM335x or Sitara AM437x processors, see *Powering the AM335x/AM437x with TPS65218* (SLVUAA9).

9.2 Typical Application

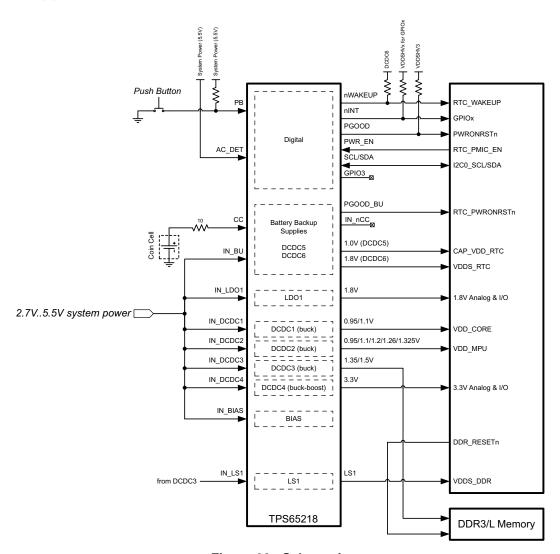


Figure 62. Schematic



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9.3 Design Requirements

	Voltage	Sequence
DCDC1	1.1 V	8
DCDC2	1.1 V	9
DCDC3	1.2 V	5
DCDC4	3.3 V	7
DCDC5	1.0 V	2
DCDC6	1.8 V	1
LDO1	1.8 V	3

9.4 Detailed Design Procedure

9.4.1 Output Filter Deisgn

The step down converters (DCDC1, DCDC2, and DCDC3) on TPS65218 are designed to operate with effective inductance values in the range of $1.0\mu\text{H}$ to $2.2\mu\text{H}$ and with effective output capacitance in the range of $10\mu\text{F}$ to $100\mu\text{F}$ The internal compensation is optimized to operate with an output filter of L = $1.5\mu\text{H}$ and Cout = $10\mu\text{F}$.

The buck boost converter (DCDC4) on TPS65218 is designed to operate with effective inductance values in the range of $1.2\mu H$ to $2.2\mu H$. The internal compensation is optimized to operate with an output filter of L = $1.5\mu H$ and Cout = $47\mu F$.

The two battery backup converters (DCDC5 and DCDC6) are designed to operate with effective inductance values in the range of $4.7\mu H$ to $22\mu H$. The internal compensation is optimized with an output filter of L = $10\mu H$ and Cout = $20\mu F$.

Larger or smaller inductor/capacitance values can be used to optimize performance of the device for specific operation conditions.

9.4.2 Inductor Selection for Buck Converters

The inductor value affects its peak to peak ripple current, the PWM to PFM transition point, the output voltage ripple, and the efficiency. The selected inductor must be rated for its DC resistance and saturation current. The inductor ripple current (Δ L) decreases with higher inductance and increases with higher Vin or Vout. Equation 1 calculates the maximum inductor current ripple under static load conditions. The saturation current of the inductor should be rated higher than the maximum inductor current as calculated with Equation 2. This is recommended as during heavy load transient the inductor current will rise above the calculated value.

$$\Delta I_L = V_{OUT} \times \frac{1 - \frac{V_{OUT}}{V_{IN}}}{L \times f} \tag{1}$$

$$I_{Lmax} = I_{OUTmax} + \frac{\Delta I_L}{2} \tag{2}$$

With:

F = Switching frequency

L = Inductor value

 ΔIL = Peak to peak inductor ripple current

I_{Lmax} = Maximum inductor current

The following inductors have been used with the TPS65218:

TEXAS INSTRUMENTS

Detailed Design Procedure (continued)

PART NUMBER	VALUE	SIZE (MM)	MANUFACTURER							
INDUCTORS FOR DCDC1, DCDC2, DCDC3, DCDC4										
SPM3012T-1R5M	1.5 μH, 2.8 A, 77 mΩ	3.2 x 3.0 x 1.2 (LxWxH)	TDK							
IHLP1212BZER1R5M11	1.5 μH, 4.0 A, 28.5 mΩ	3.6 x 3.0 x 2.0 (LxWxH)	Vishay							
INDUCTORS FOR DCDC5, DCDC	INDUCTORS FOR DCDC5, DCDC6									
MLZ2012N100L	10 μH, 110 mA, 300 mΩ	2012 / 0805 (2.00 x 1.25 x 1.25 LxWxH)	TDK							
LQM21FN100M80	10 μH, 100 mA, 300 mΩ	2012 / 0805 (2.00 x 1.25 x 1.25 LxWxH)	Murata							

9.4.3 Output Capacitor Selection

The hysteretic PWM control scheme of the TPS65218 switching converters allows the use of tiny ceramic capacitors. Ceramic capacitors with low ESR values have the lowest output voltage ripple and are recommended. The output capacitor requires either an X7R or X5R dielectric.

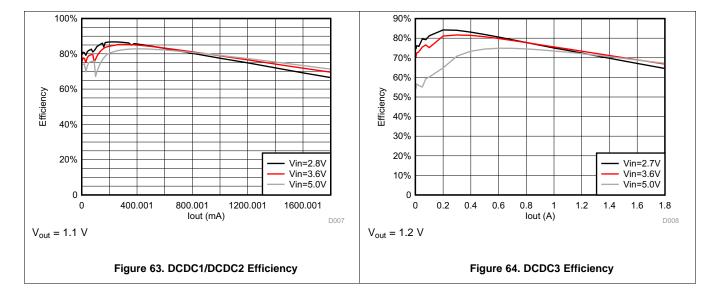
At light load currents the converter operates in Power Save Mode, and the output voltage ripple is dependent on the output capacitor value and the PFM peak inductor current. Higher output capacitor values minimize the voltage ripple in PFM Mode and tighten DC output accuracy in PFM Mode.

The two battery backup converters (DCDC5 and DCDC6) always operate in PFM mode. For these converters at least 20 uF is recommended on the output to help minimize voltage ripple.

The Buck-Boost converter requires additional output capacitance to help maintain converter stability during high load conditions. At least 40 uF of output capacitance is recommended and an additional 100 nF capacitor can be added to further filter output ripple.

9.5 Application Curves

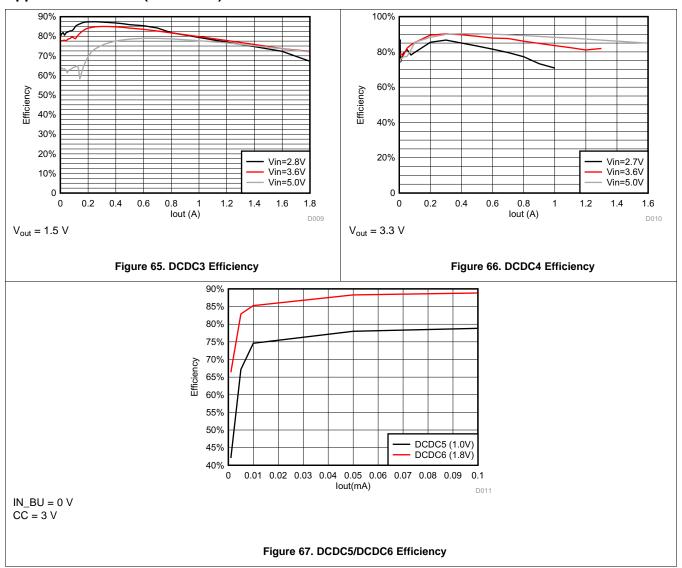
At T_J=25°C unless otherwise noted





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Application Curves (continued)



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TEXAS INSTRUMENTS

10 Power Supply Recommendations

The device is designed to operate with an input voltage supply range between 2.7V and 5.5V. This input supply can be from a single cell Li-lon battery or other externally regulated supply. If the input supply is located more than a few inches from the TPS65218 additional bulk capacitance may be required in addition to the ceramic bypass capacitors. An electrolytic capacitor with a value of 47uF is a typical choice.

The coin cell back up input is designed to operate with a input voltage supply between 2.2V and 3.3V This input should be supplied by a coin cell battery with 3V nominal voltage.

11 Layout

11.1 Layout Guidelines

- The IN_X pins should be bypassed to ground with a low ESR ceramic bypass capacitor. The typical recommended bypass capacitance is 4.7-µF with a X5R or X7R dielectric.
- The optimum placement is closest to the IN_X pins of the device. Care should be taken to minimize the the loop area formed by the bypass capacitor connection, the IN_X pin, and the Power Pad of the device.
- The Power Pad should be tied to the PCB ground plane with multiple vias.
- The LX trace should be kept on the PCB top layer and free of any vias.
- The FBX traces should be routed away from any potential noise source to avoid coupling.
- DCDC4 Output capacitance should be placed imediately at the DCDC4 pin. Excessive distance between the capacitance and DCDC4 pin may cause poor converter performance.

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11.2 Layout Example

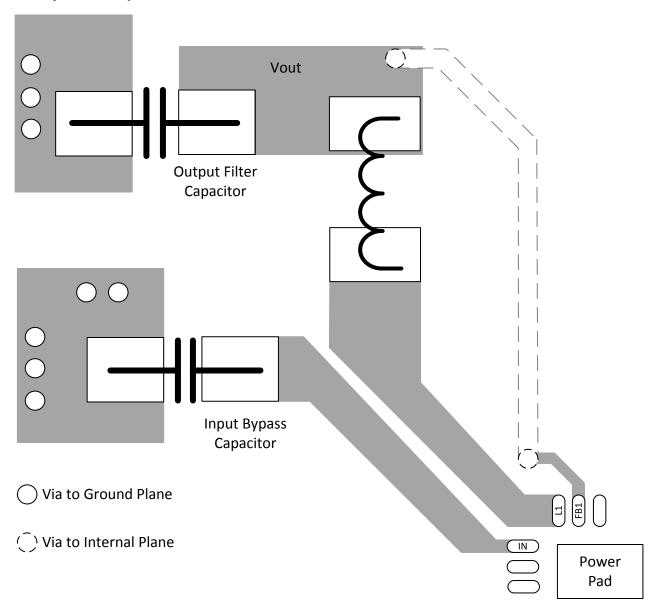


Figure 68. Layout Example

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12 Device and Documentation Support

12.1 Trademarks

12.2 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.3 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.





27-Nov-2014

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TPS65218B1PHPR	ACTIVE	HTQFP	PHP	48	1000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 105	T65218B1	Samples
TPS65218B1PHPT	ACTIVE	HTQFP	PHP	48	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 105	T65218B1	Samples
TPS65218B1RSLR	ACTIVE	VQFN	RSL	48	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 105	TPS 65218B1	Samples
TPS65218B1RSLT	ACTIVE	VQFN	RSL	48	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 105	TPS 65218B1	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.



PACKAGE OPTION ADDENDUM

27-Nov-2014

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
BO	Dimension designed to accommodate the component length
	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

All differsions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS65218B1PHPR	HTQFP	PHP	48	1000	330.0	16.4	9.6	9.6	1.5	12.0	16.0	Q2
TPS65218B1PHPT	HTQFP	PHP	48	250	330.0	16.4	9.6	9.6	1.5	12.0	16.0	Q2
TPS65218B1RSLR	VQFN	RSL	48	2500	330.0	16.4	6.3	6.3	1.1	12.0	16.0	Q2
TPS65218B1RSLT	VQFN	RSL	48	250	180.0	16.4	6.3	6.3	1.1	12.0	16.0	Q2

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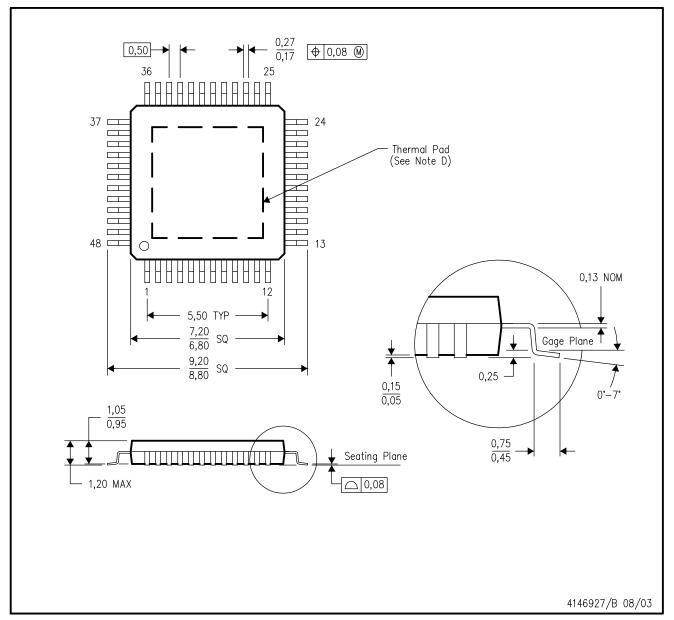


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS65218B1PHPR	HTQFP	PHP	48	1000	336.6	336.6	31.8
TPS65218B1PHPT	HTQFP	PHP	48	250	336.6	336.6	31.8
TPS65218B1RSLR	VQFN	RSL	48	2500	367.0	367.0	38.0
TPS65218B1RSLT	VQFN	RSL	48	250	210.0	185.0	35.0

PHP (S-PQFP-G48)

PowerPAD™ PLASTIC QUAD FLATPACK



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com www.ti.com.
- E. Falls within JEDEC MS-026

PowerPAD is a trademark of Texas Instruments.



PHP (S-PQFP-G48)

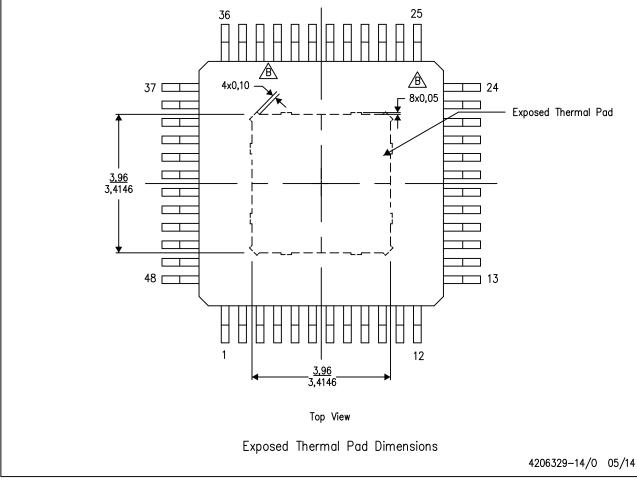
PowerPAD™ PLASTIC QUAD FLATPACK

THERMAL INFORMATION

This PowerPAD $^{\mathbf{m}}$ package incorporates an exposed thermal pad that is designed to be attached to a printed circuit board (PCB). The thermal pad must be soldered directly to the PCB. After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.

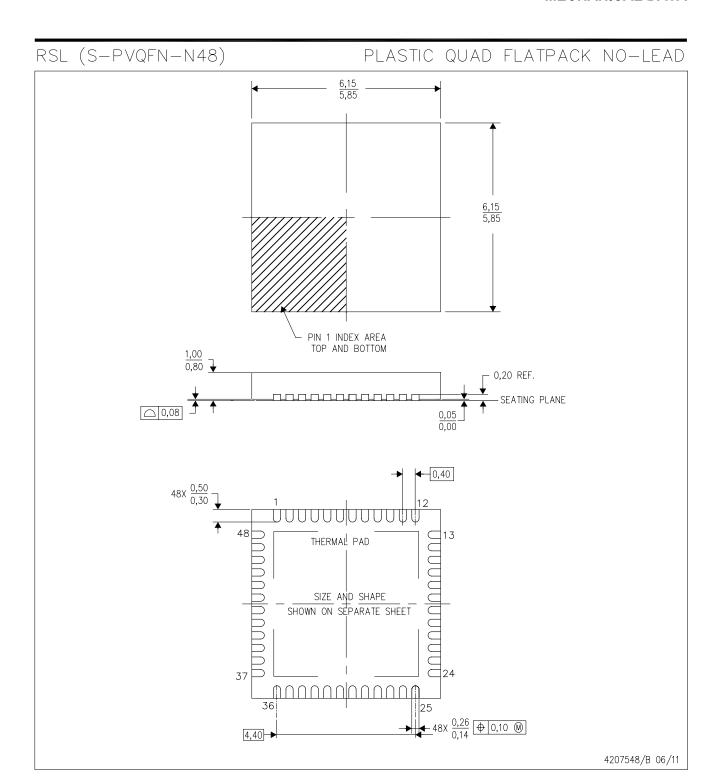


NOTE: A. All linear dimensions are in millimeters

\(\hat{\text{P}} \) Tie strap features may not be present.

PowerPAD is a trademark of Texas Instruments





NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.

- B. This drawing is subject to change without notice.
- C. Quad Flatpack, No-leads (QFN) package configuration.
- D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.



RSL (S-PVQFN-N48)

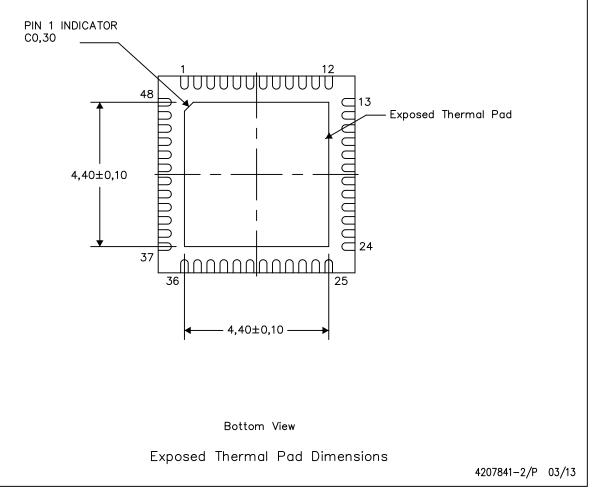
PLASTIC QUAD FLATPACK NO-LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No—Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

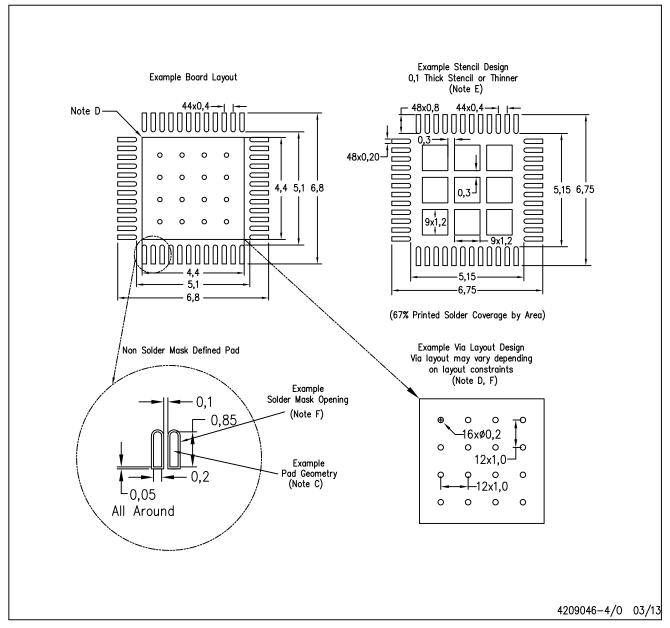
The exposed thermal pad dimensions for this package are shown in the following illustration.



NOTE: All linear dimensions are in millimeters

RSL (S-PVQFN-N48)

PLASTIC QUAD FLATPACK NO-LEAD



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com http://www.ti.com.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for recommended solder mask tolerances and via tenting recommendations for vias placed in the thermal pad.



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